



Od pomysłu do zwycięstwa – nasz sukces w International Future Energy Challenge 2025

Hardware Design Masterclasses, 28.11.2025

Paweł Wodzyński



Faculty of Electrical Engineering

Warsaw University of Technology

Agenda

1. Czym jest IFEC?
2. Tematyka konkursu
3. Nasz zespół – jak to się zaczęło
4. W stronę zwycięstwa na Tajwanie
5. Nasze rozwiązanie
6. Proces projektowania
7. Finalne wyniki
8. Q&A



International Future Energy Challenge

- Największy międzynarodowy konkurs studencki
- Ponad 20 lat tradycji
- Współpraca z przemysłem
- Wspierany przez największe organizacje



Tematyka poprzednich edycji International Future Energy Challenge

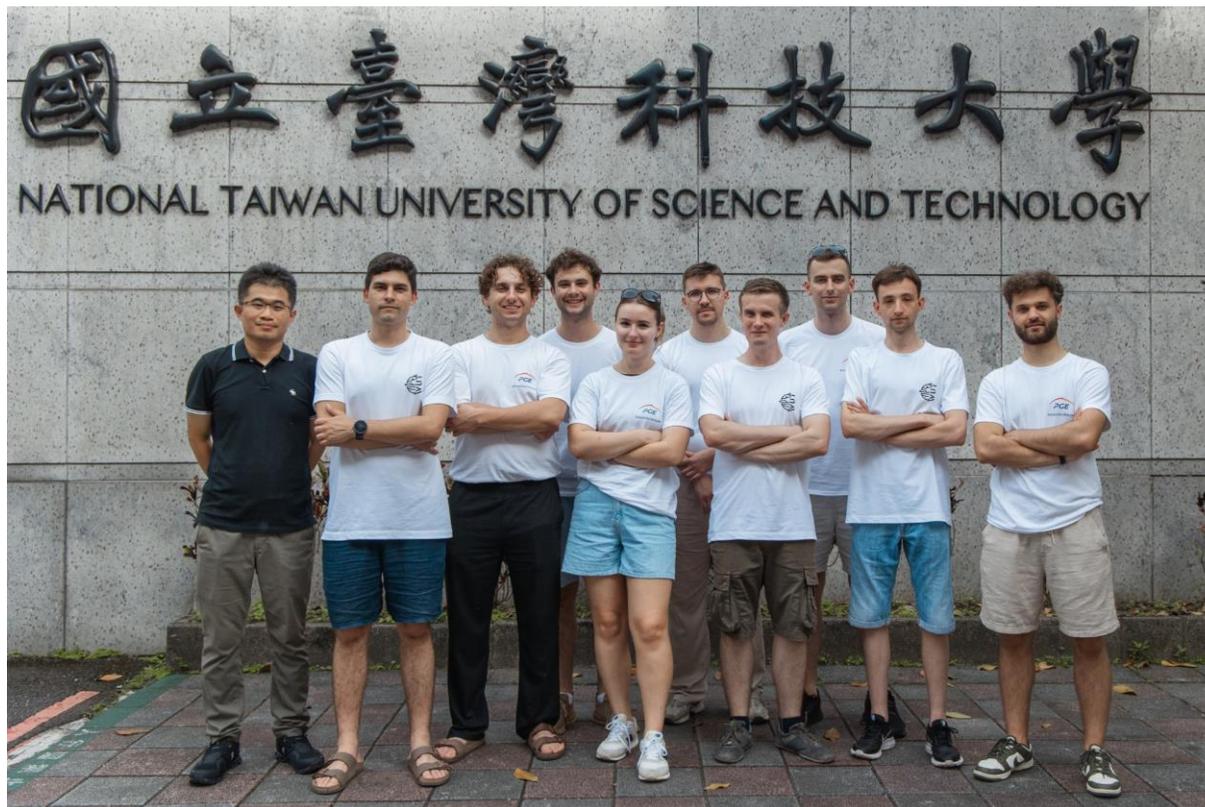
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- 2021 Power Supply for Nano Satelites
 - 2022 Smart, Efficient and Light Solar Microgrid Inverter
 - 2023 Single-Phase Solid State Transformer
 - 2024 Audio amplifier
 - 2025 Isolated DC-DC Converter with Fast Transient Response and Low Noise**
 - 2026 Affordable Bidirectional Onboard Charger for Electric Vehicles



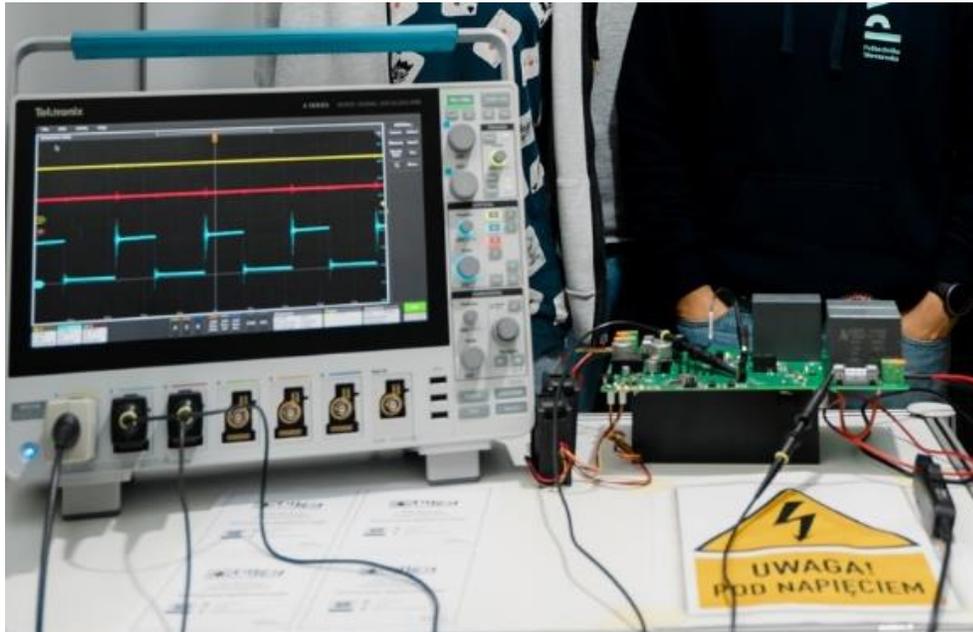
Koło Naukowe Drones Renewables



Koło Naukowe Power Electronics And Plasma Applications

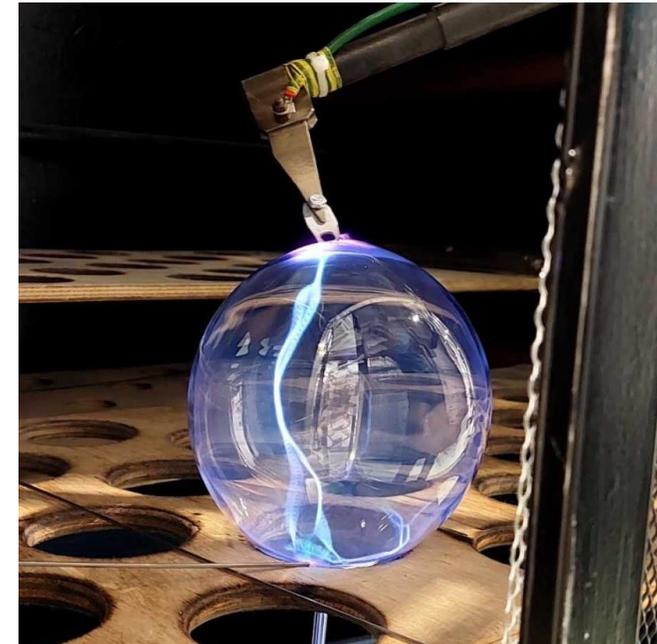


Koło Naukowe Drones Renewables



Mobilna stacja ładowania dronów

Koło Naukowe Power Electronics And Plasma Applications



Wzbudzenie plazmy za pomocą wysokoczęstotliwościowego przekształtnika

Zespół IFEC



Mgr inż. Krzysztof
Kalinowski



Od lewej:
Tomasz Zakrzewski
Przemysław Kinasz
Jakub Pykacz
Adrian Ośka

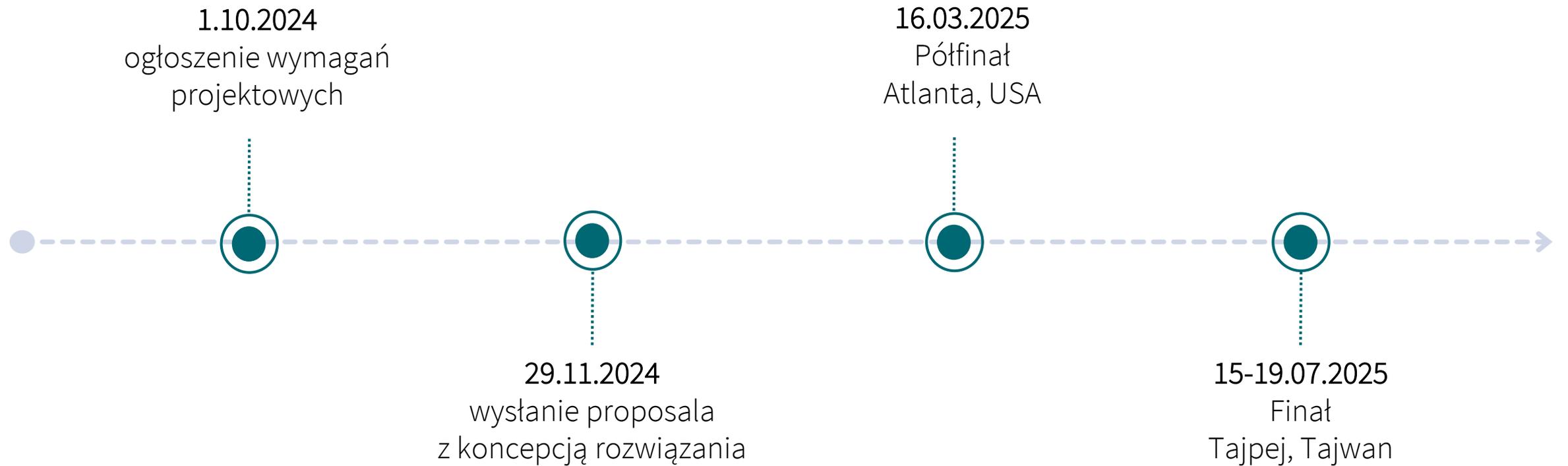
Michał Ptak
Krzysztof Kalinowski
Adrianna Machulak
Paweł Wodzyński
Natalia Wnęk
Błażej Skrzypkowski



Prof. dr hab. inż. Jacek
Rąbkowski



Etapy konkursu IFEC 2025



Półfinał konkursu w Atlancie, USA – 13 zespołów z 9 krajów



Półfinał konkursu w Atlancie, USA – konferencja APEC



Zespoły IFEC 2025

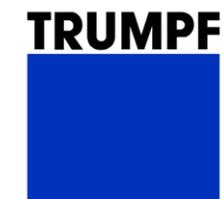
University	Country
Bharatiya Vidya Bhavan's Sardar Patel Institute of Technology	India
KU Leuven and UHasselt (Hasselt University)	Belgium
Huazhong University of Science and Technology	China
Konkuk University	South Korea
National Formosa University	Taiwan
National Kaohsiung University of Science and Technology	Taiwan
Reutlingen University	Germany
The University of Connecticut	United States
University of Belgrade	Serbia
University of Rhode Island	United States
University of Texas at Austin	United States
Utah State University	United States
Warsaw University of Technology	Poland



Finansowanie zewnętrzne



JitTeam™
the human factor
of IT



FUNDACJA GRUPY



Finał na Tajwanie – Chroma ATE



Grand Prize
Warsaw University of Technology,
Poland

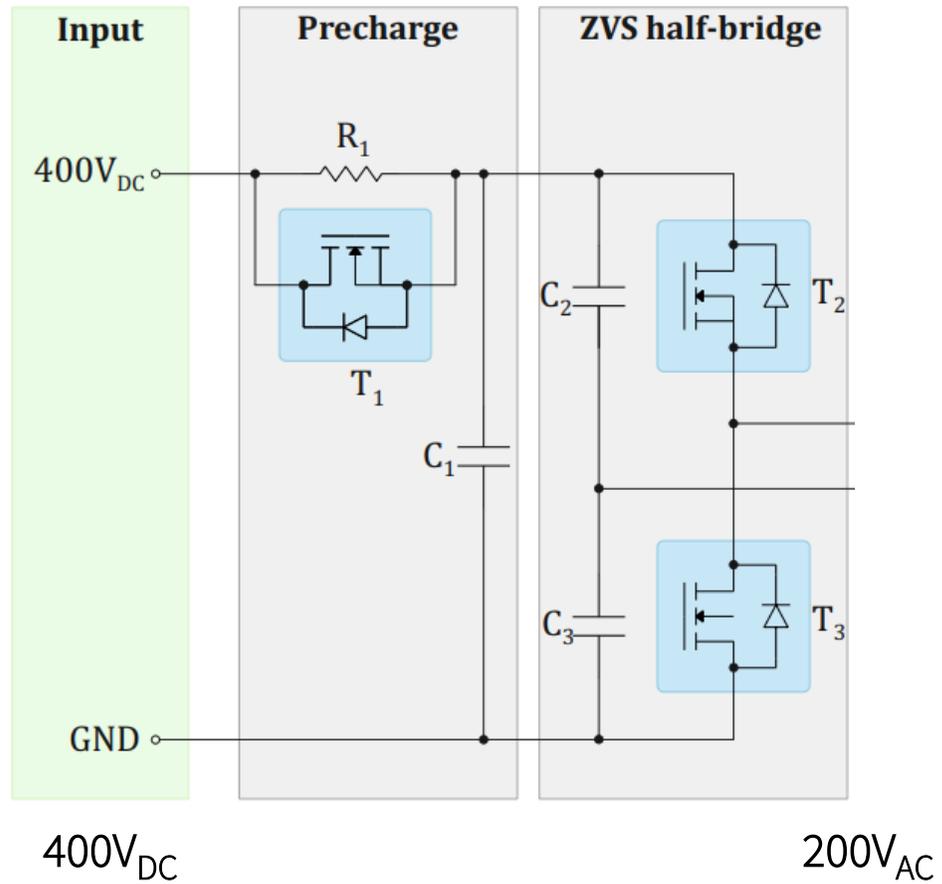


Wytyczne - Isolated DC-DC Converter with Fast Transient Response and Low Noise

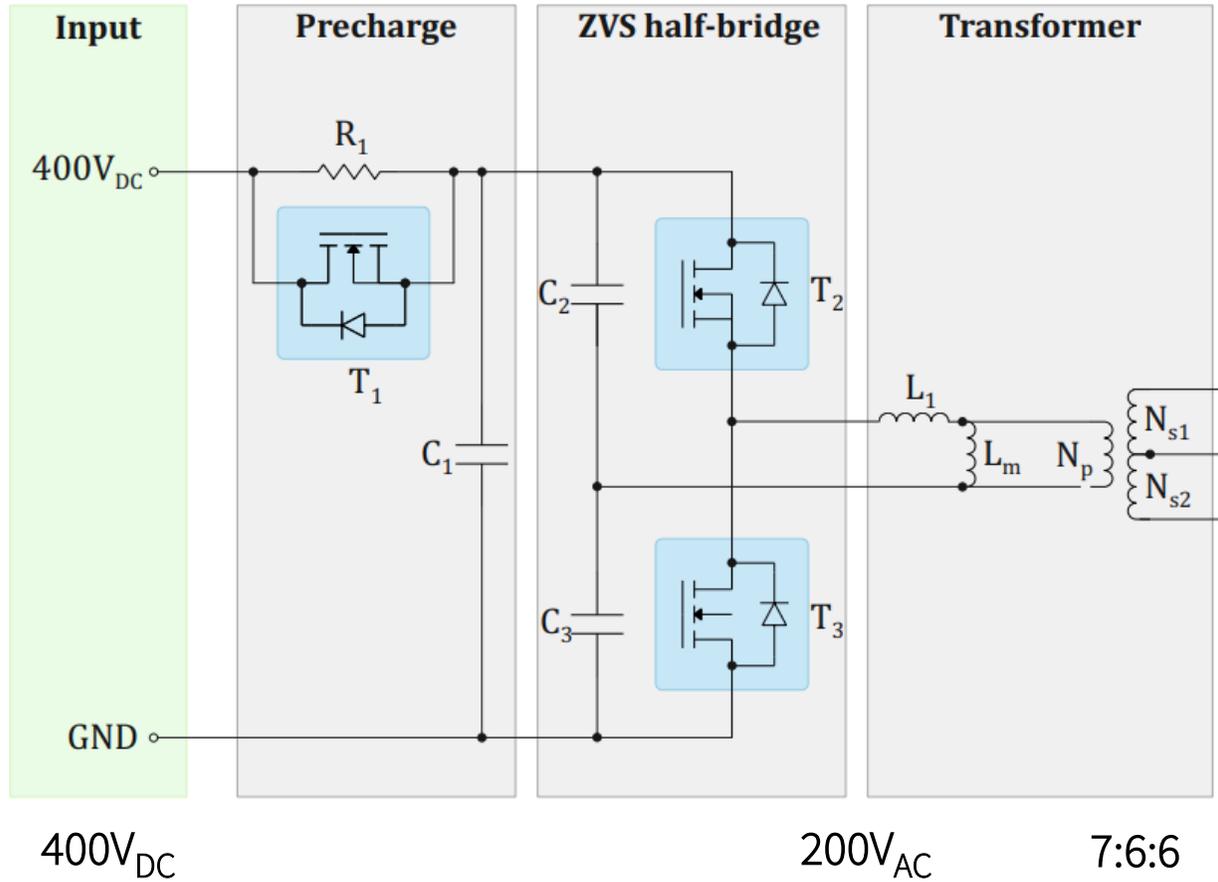
 Input Voltage 400Vdc (400–600μF @ ≥450V)	Output Voltage 20–150Vdc (<0.5% accuracy)	Output Current Max 10Adc
 Rated Power 1.5kW@150V, 600W@60V, 200W@20V	Load Response ±200mV within 100μs (0–10A)	 Step Response Rise <100μs, Fall <1ms
Regulation <0.1% @ 20V, 60V, 150V	 Ripple & Noise <200mVp-p/30mVrms (20MHz BW)	Efficiency >92%@25%, >96%@50%, >95%@100%
 Power Density >1.6W/cm ³	OCP & OL 12 A for 2s ≥13 A - OFF (< 100ms)	Thermal & Safety Air cooling only No burn-in damage (150V, 10min, 60°C±5) Galvanic isolation 1.5kVac



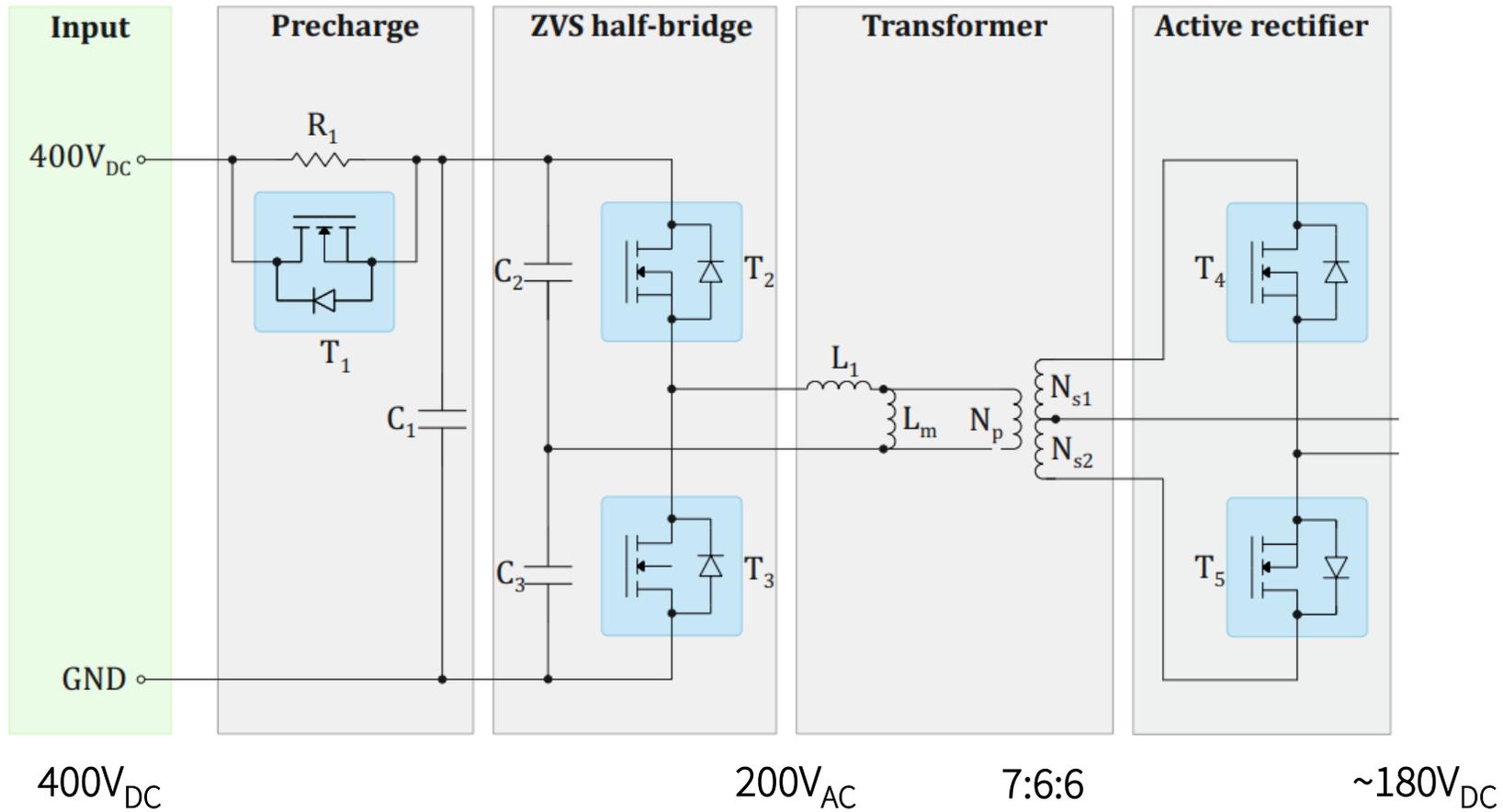
Konceptcja techniczna



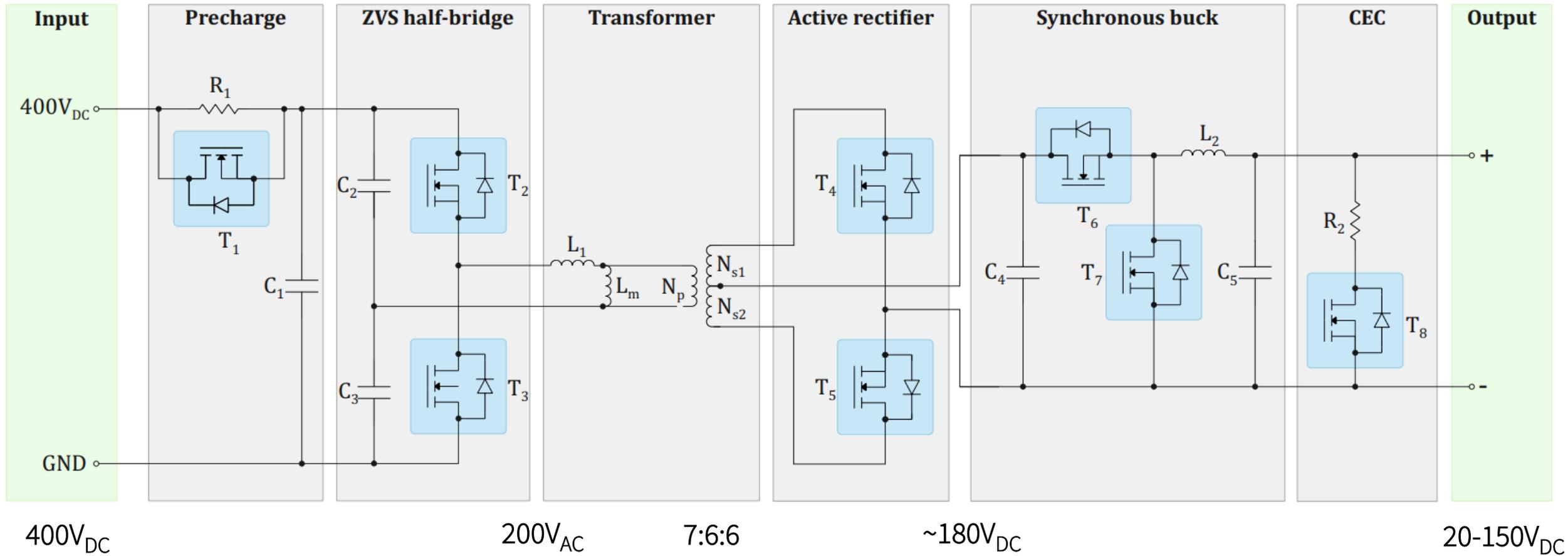
Konceptcja techniczna



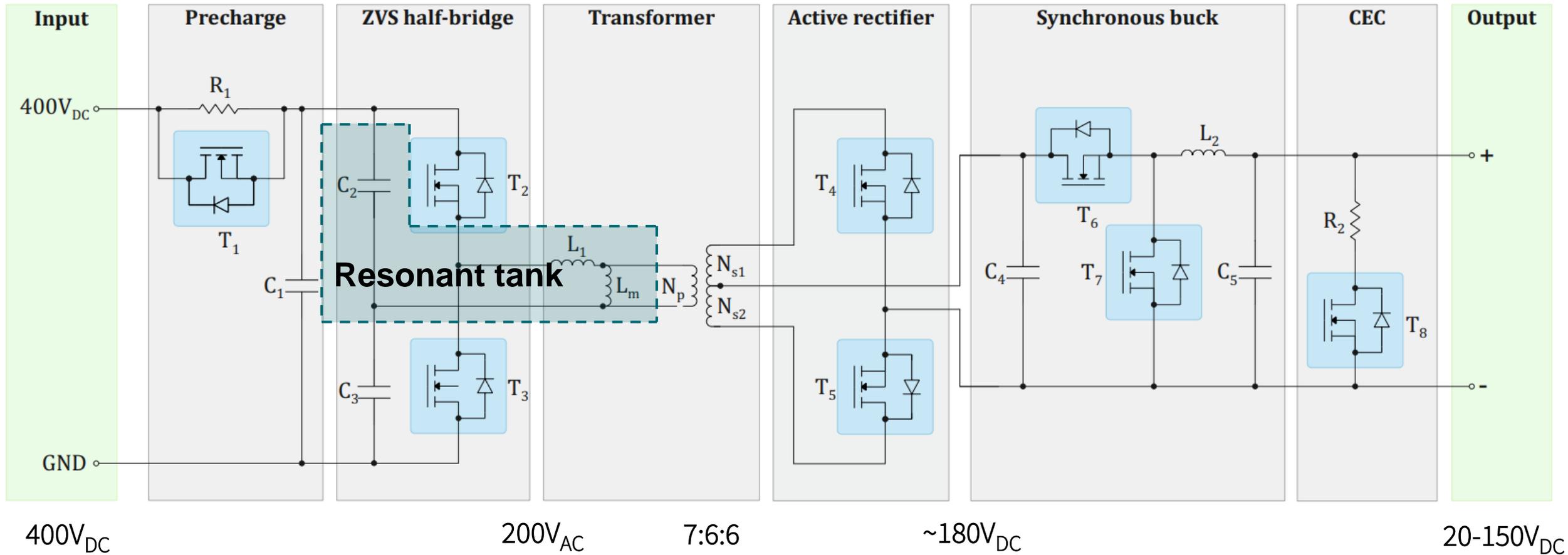
Konceptcja techniczna



Konceptcja techniczna

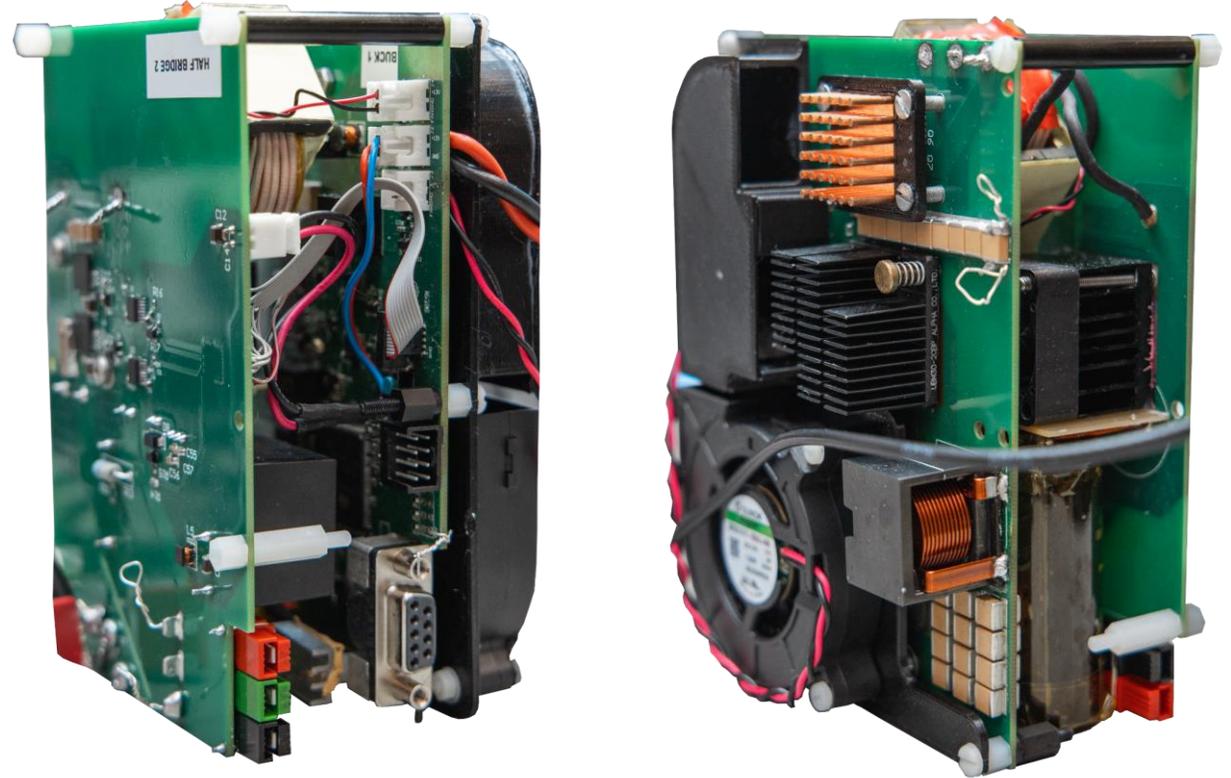


Konceptcja techniczna

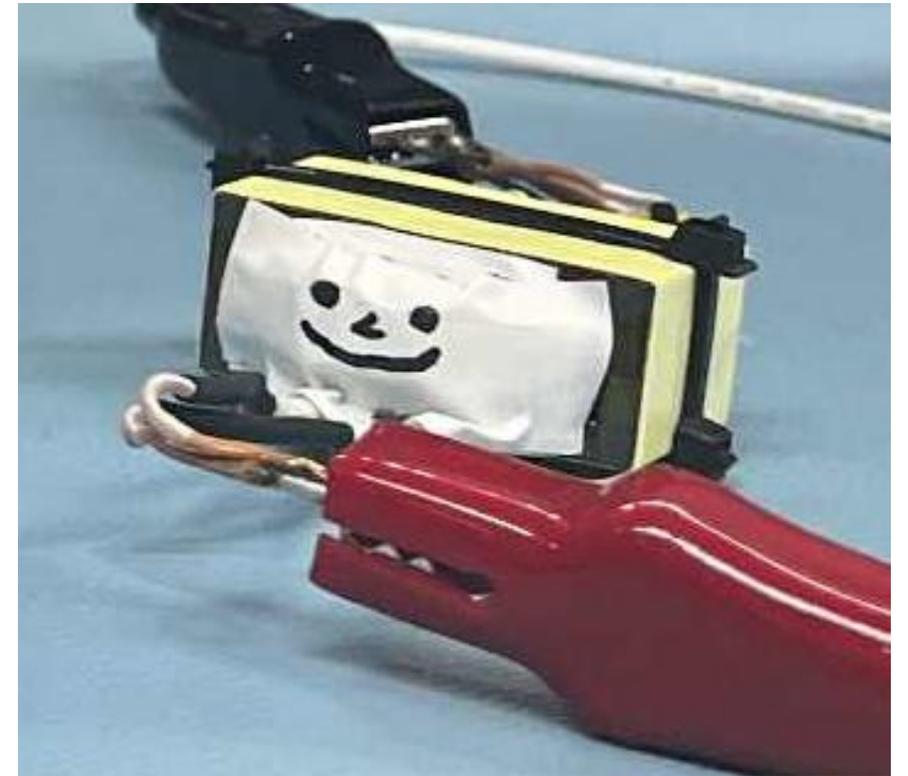
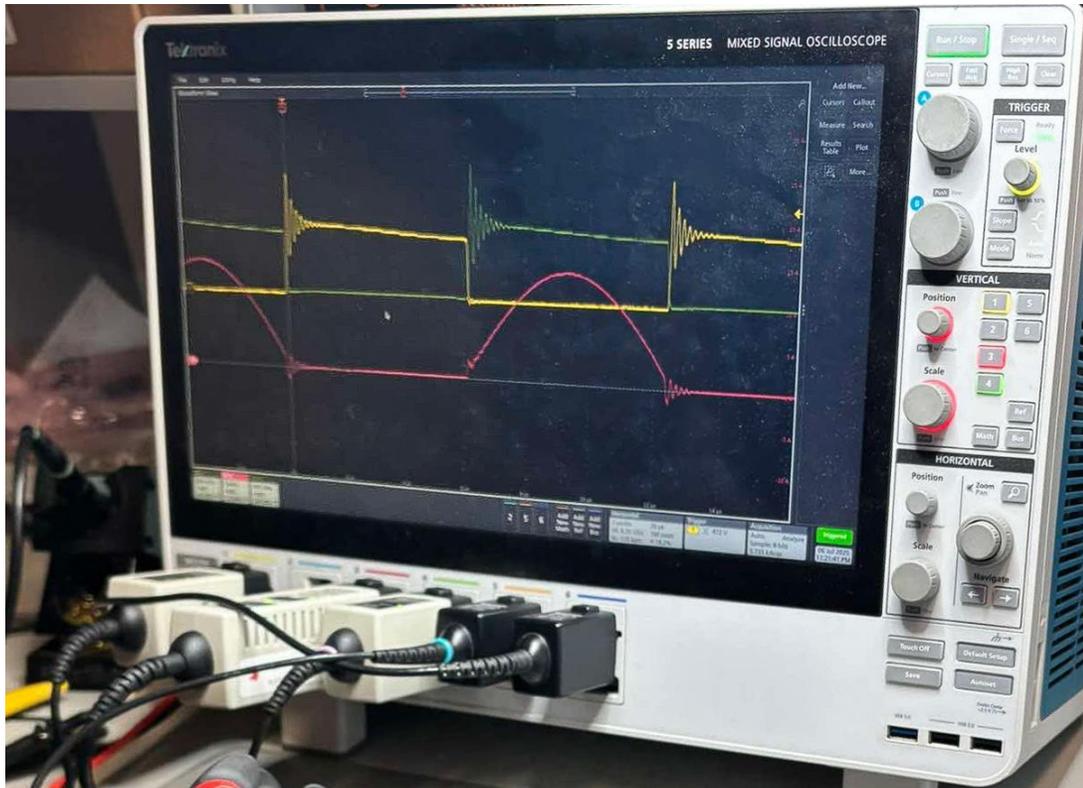


Finalna koncepcja projektowa

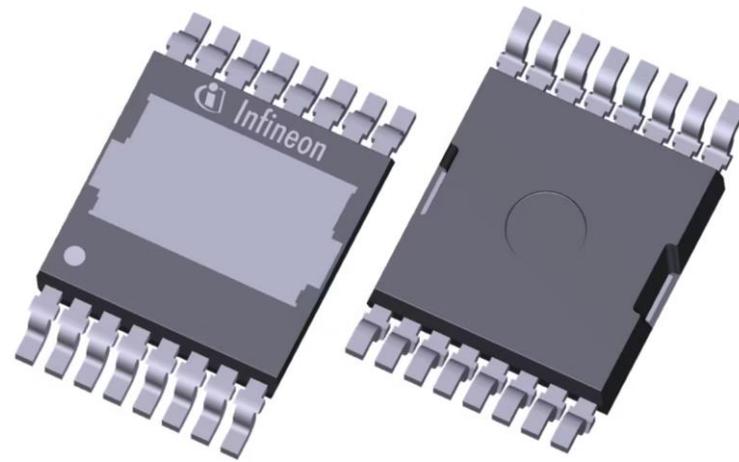
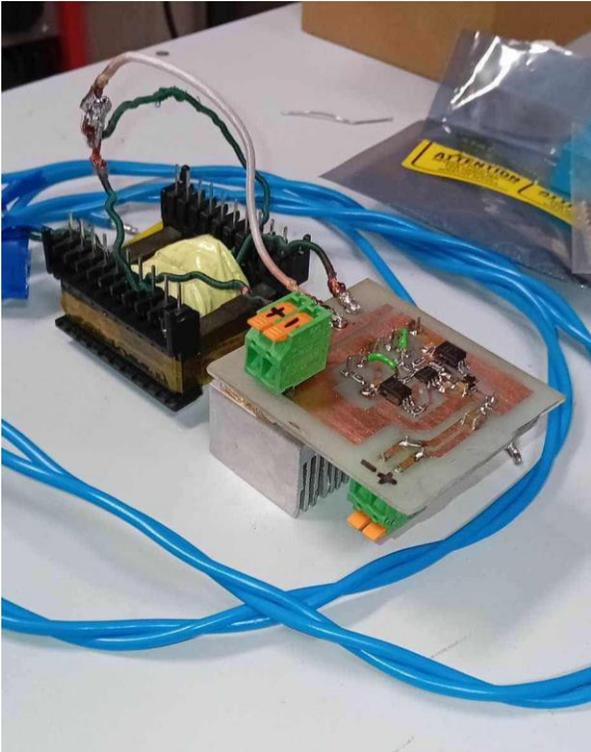
- 2 stopnie konwersji
 - 1. stopień – GaN half-bridge with SiC rectifier (80 kHz)
 - 2. stopień – GaN Synchronous Buck (200 kHz)
- sterowanie oparte na STM32H7 (dual core)
- nisko-profilowy transformator
- system dwukanałowego chłodzenia powietrzem
- kompaktowy kształt



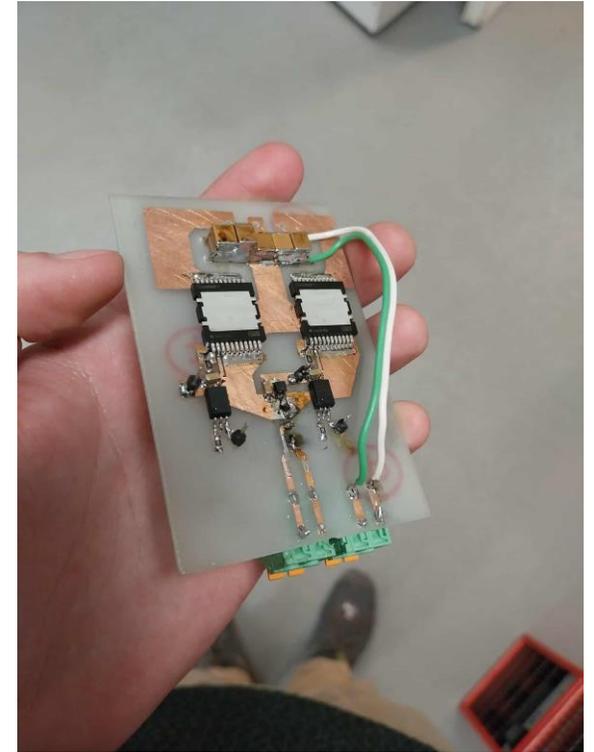
Optimalizacja sprawności



Proces prototypowania prostownika aktywnego



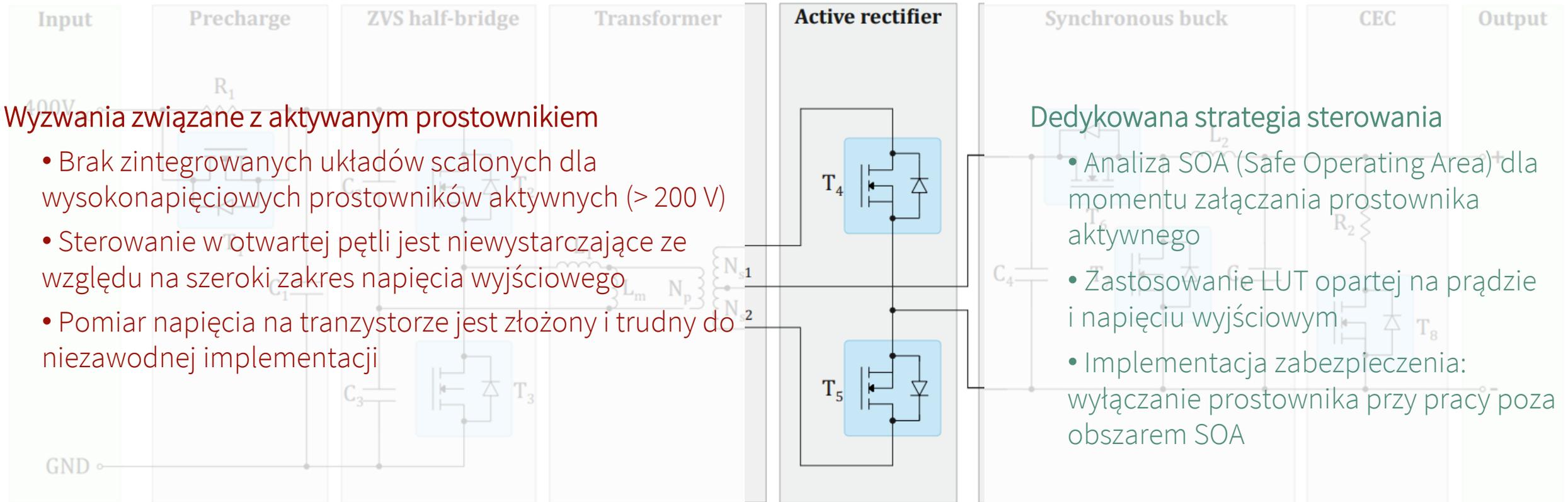
IMLT65R026M2H



Sterowanie prostownika aktywnego

Wyzwania związane z aktywnym prostownikiem

- Brak zintegrowanych układów scalonych dla wysokonapięciowych prostowników aktywnych (> 200 V)
- Sterowanie w otwartej pętli jest niewystarczające ze względu na szeroki zakres napięcia wyjściowego
- Pomiar napięcia na tranzystorze jest złożony i trudny do niezawodnej implementacji

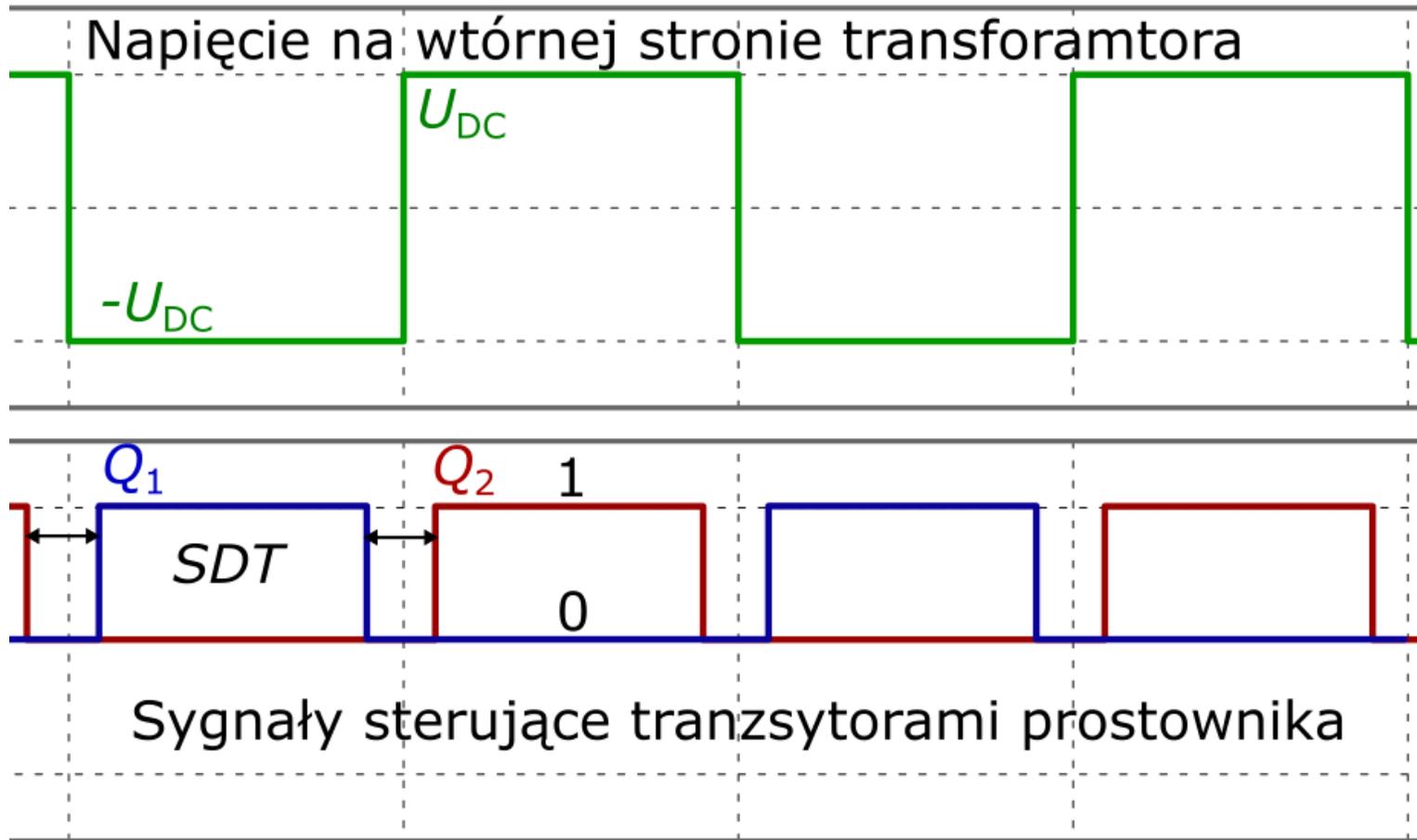


Dedykowana strategia sterowania

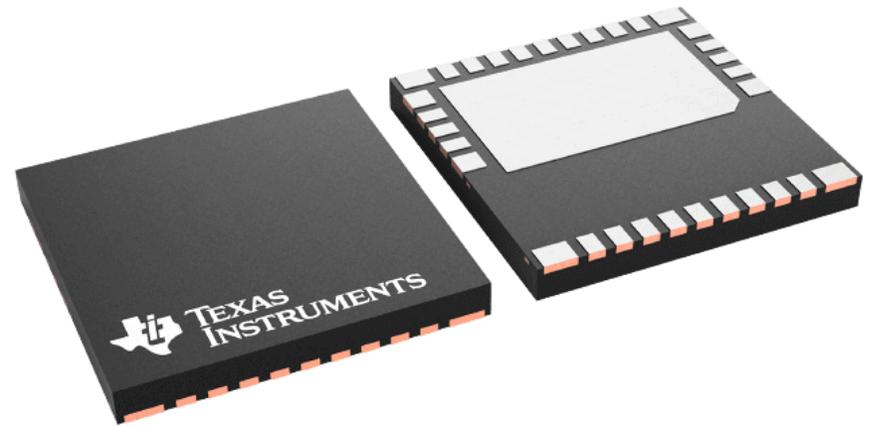
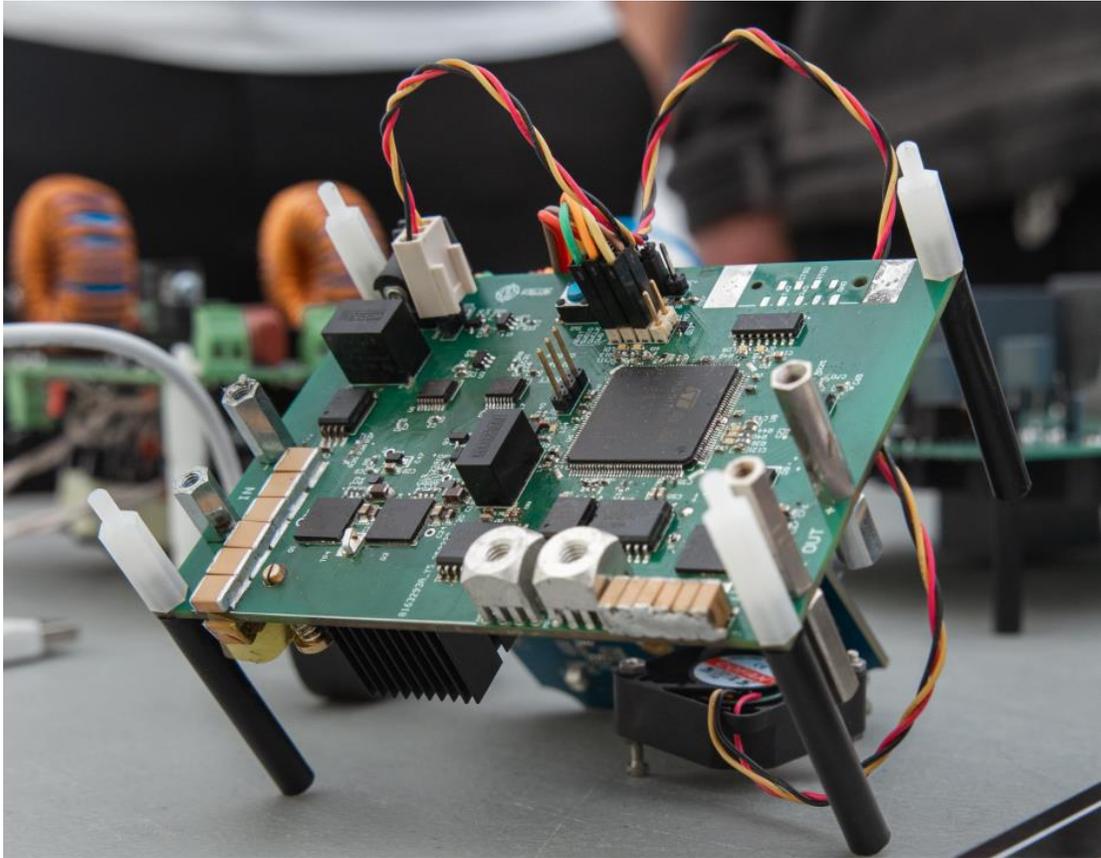
- Analiza SOA (Safe Operating Area) dla momentu załączania prostownika aktywnego
- Zastosowanie LUT opartej na prądzie i napięciu wyjściowym
- Implementacja zabezpieczenia: wyłączenie prostownika przy pracy poza obszarem SOA



Sterowanie prostownika aktywnego

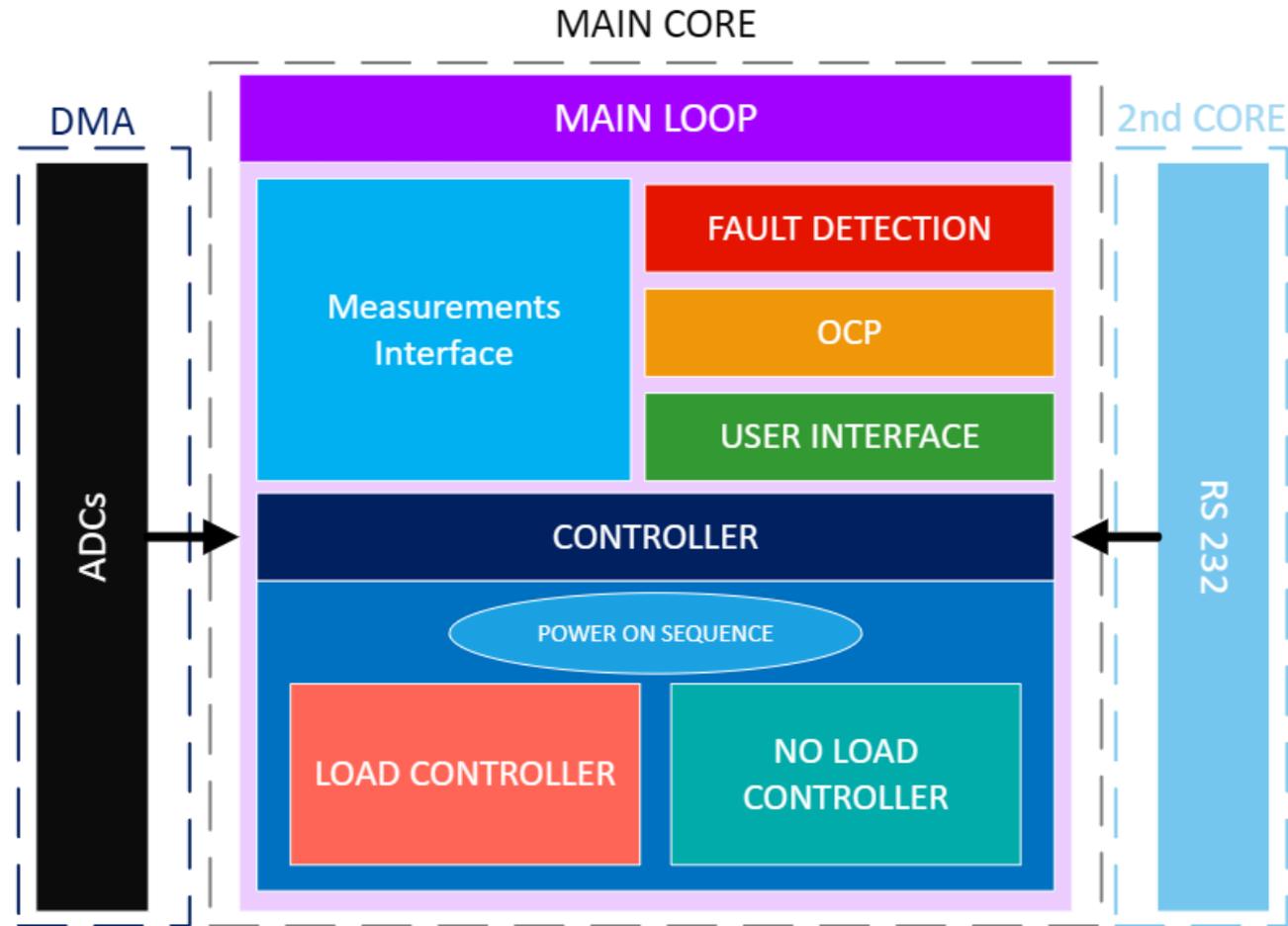


Półprzewodniki

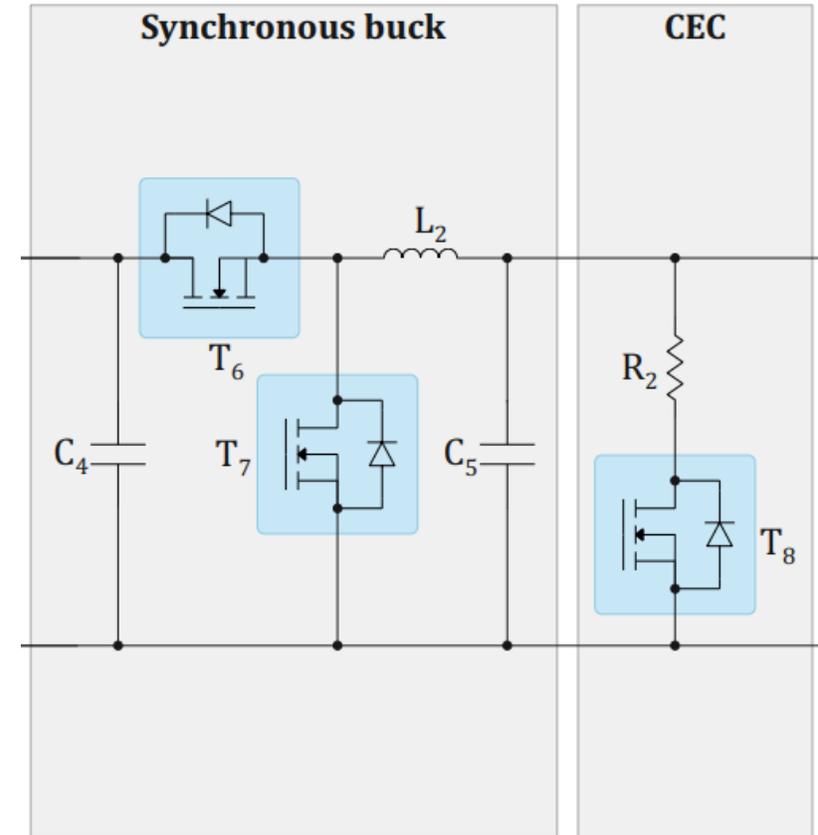
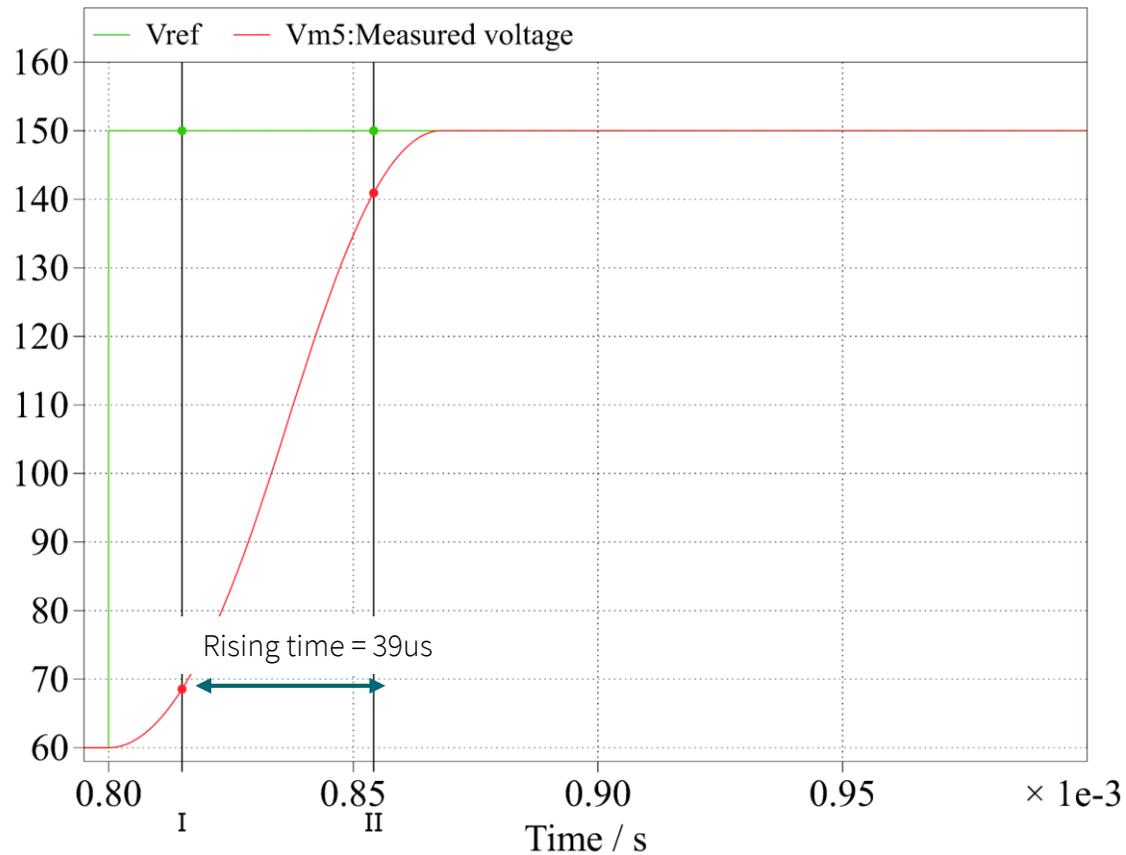


LMG3411R050RWHT

Układ sterowania



Sterowanie w stanach bez obciążenia



Finał na Tajwanie – Chroma ATE

1. Electrical tests

- Step response of output voltage
- Dynamic performance
- Voltage accuracy & load regulation
- Voltage noise & ripple
- Conversion efficiency
- Protection function validation

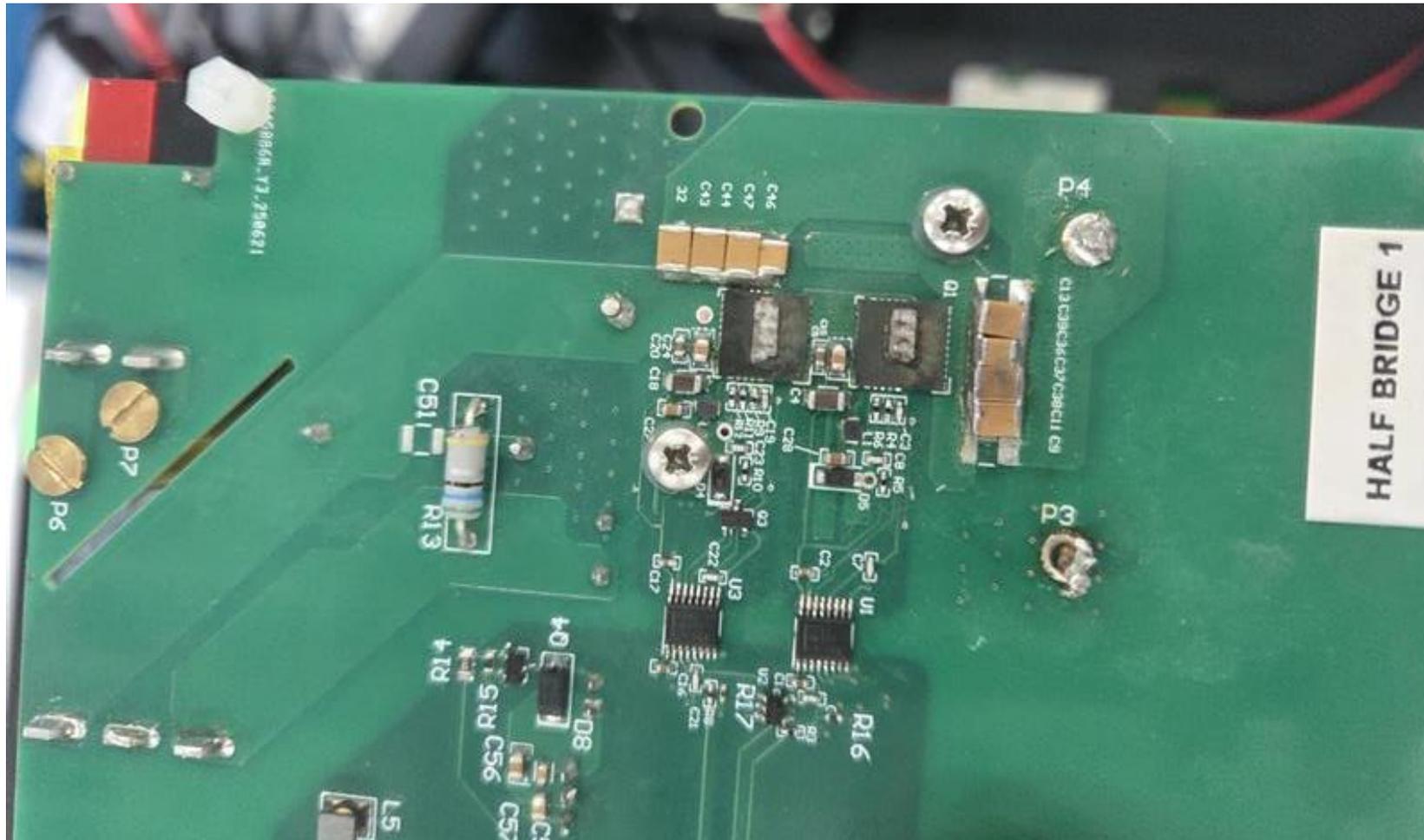
2. Burn-in test

3. Safety test (Hi-pot test)

4. Physical characteristics and design objectives

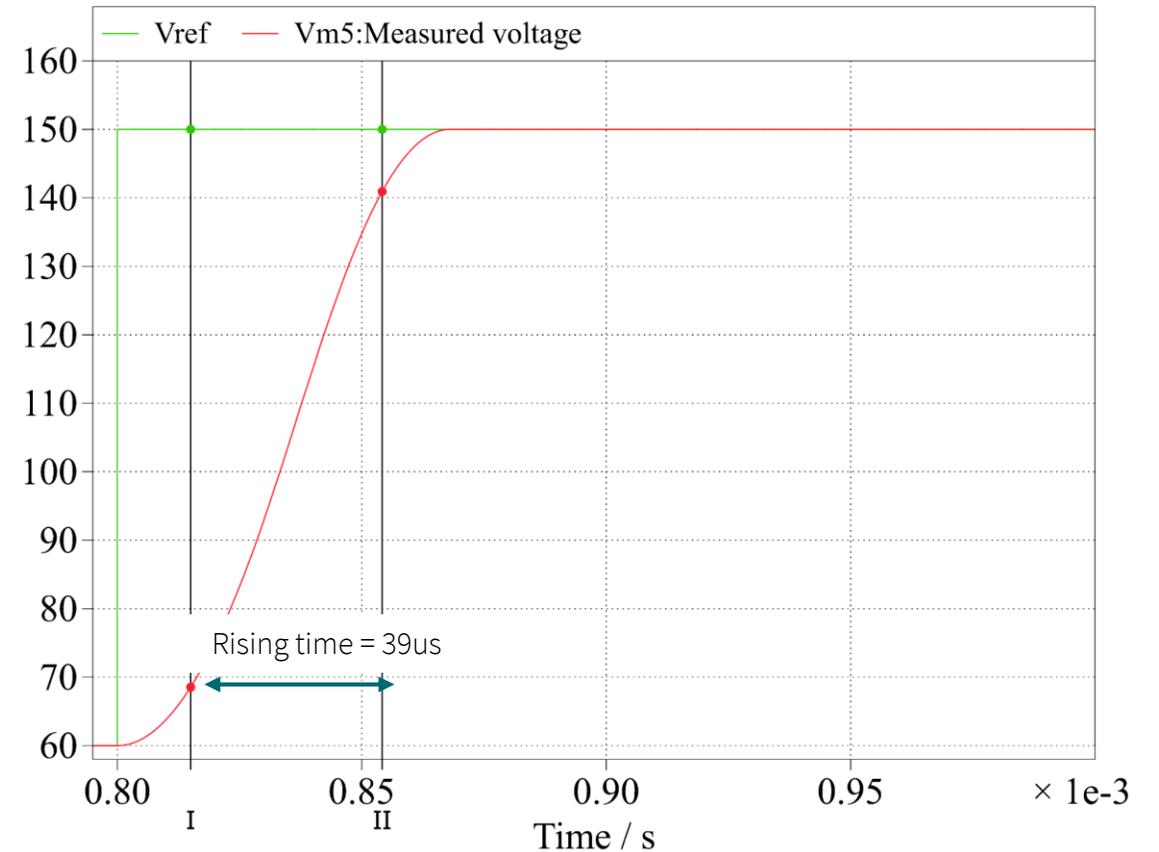
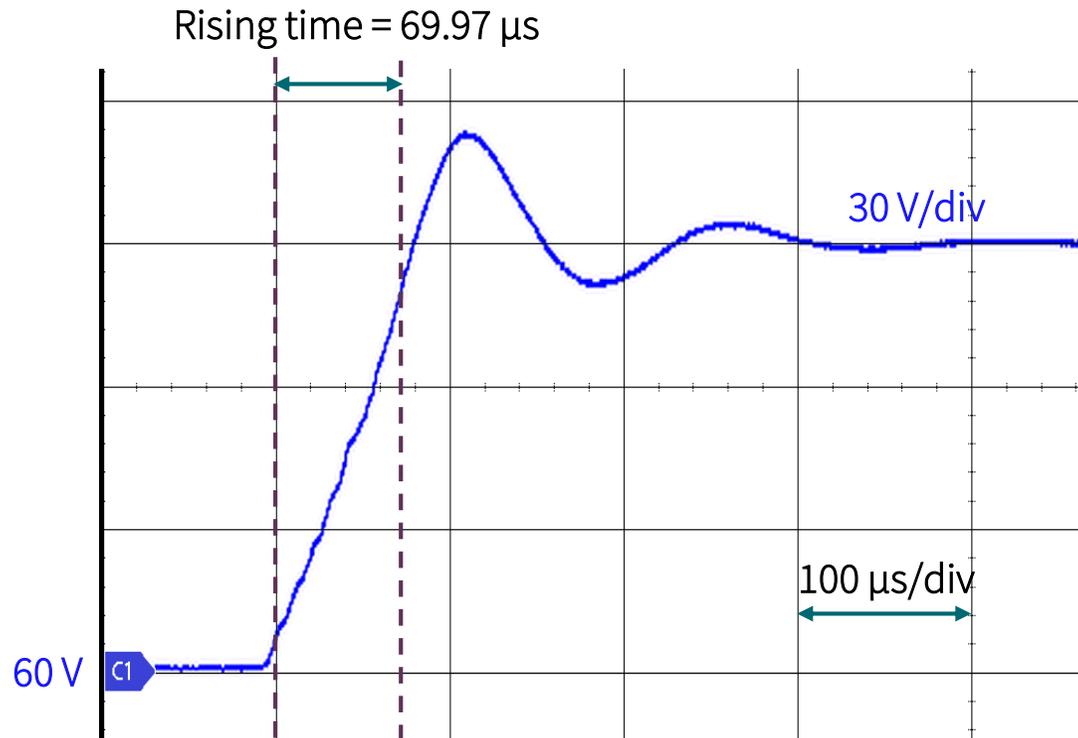


Finał na Tajwanie – falstart

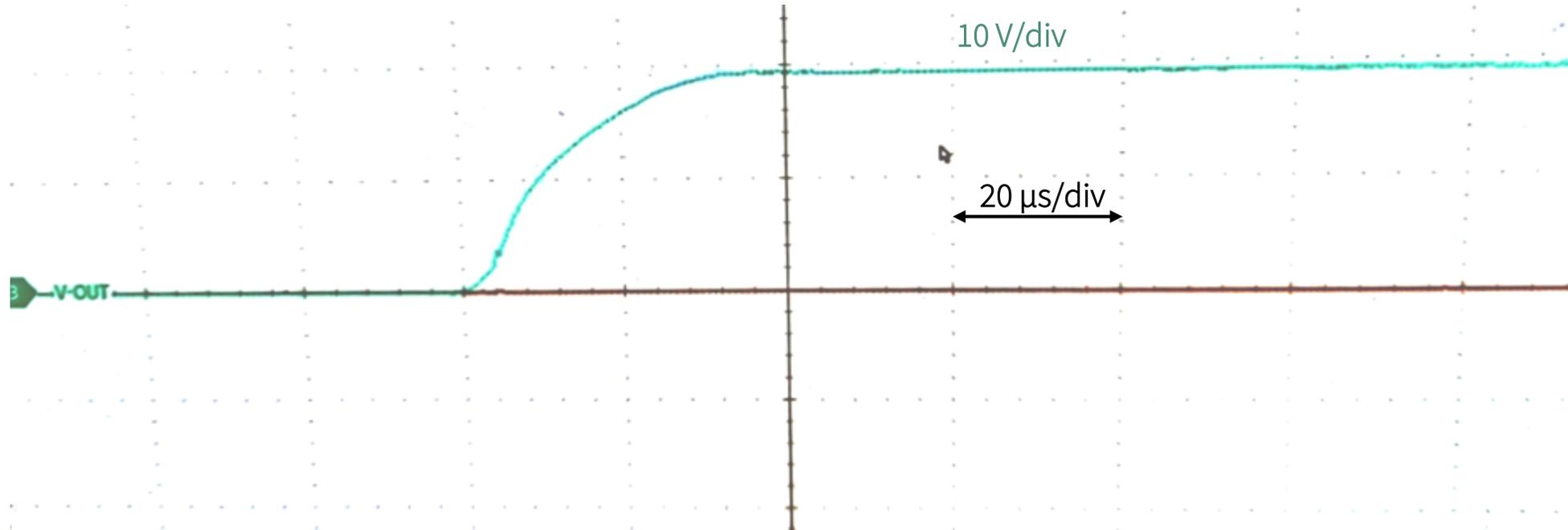


Wyniki pomiarów

Step response of output voltage – 60 V → 150 V (No load)

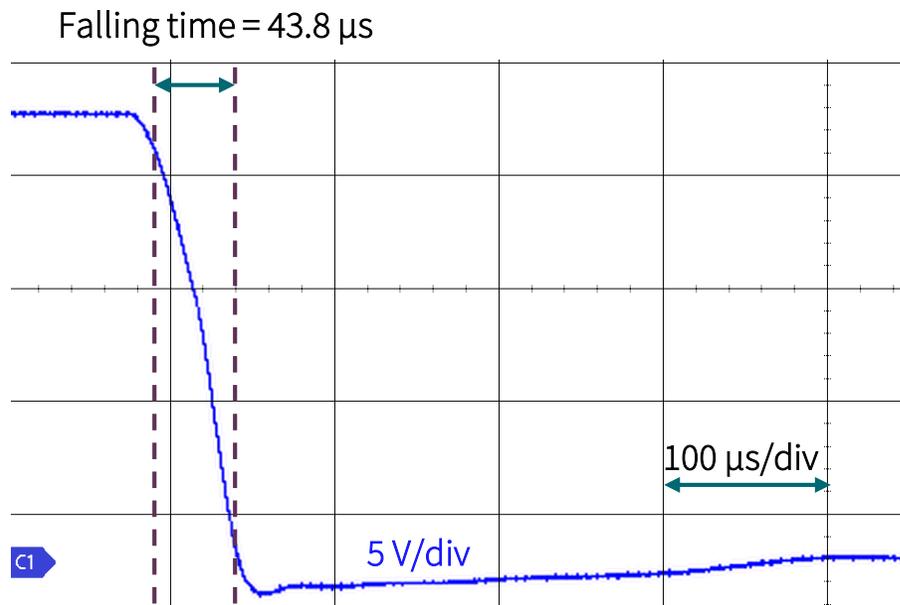


Step response of output voltage – 0 V → 20 V

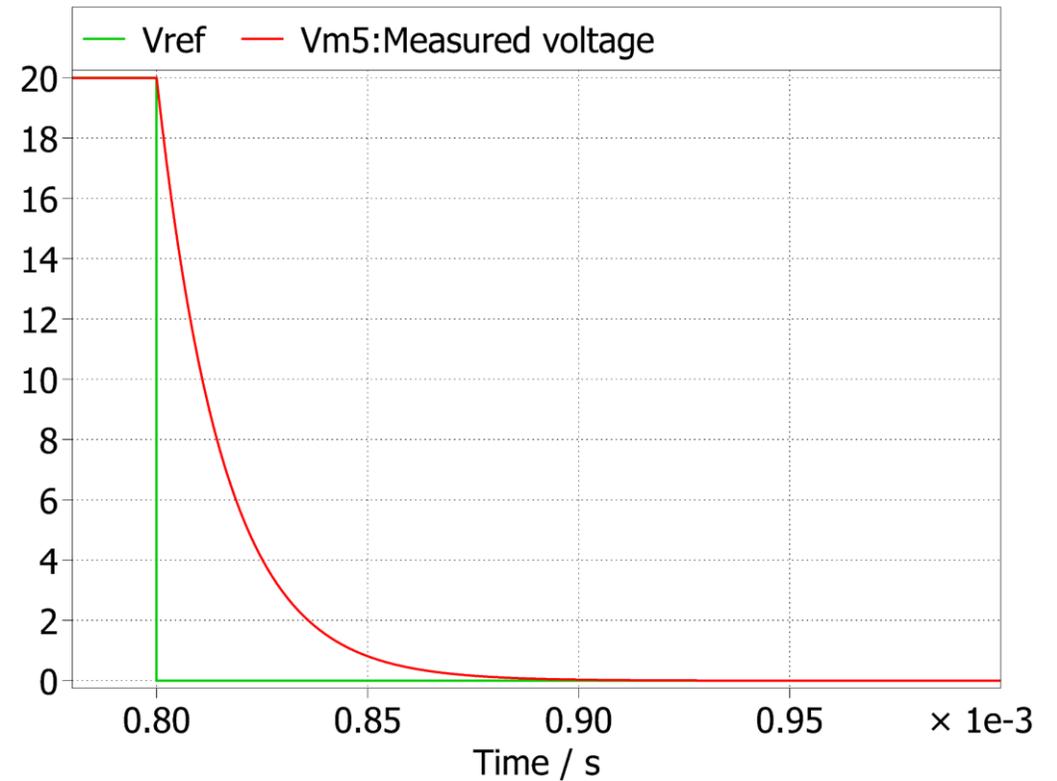


Step response of output voltage – 20 V → 0 V

Measurement results



Simulation results



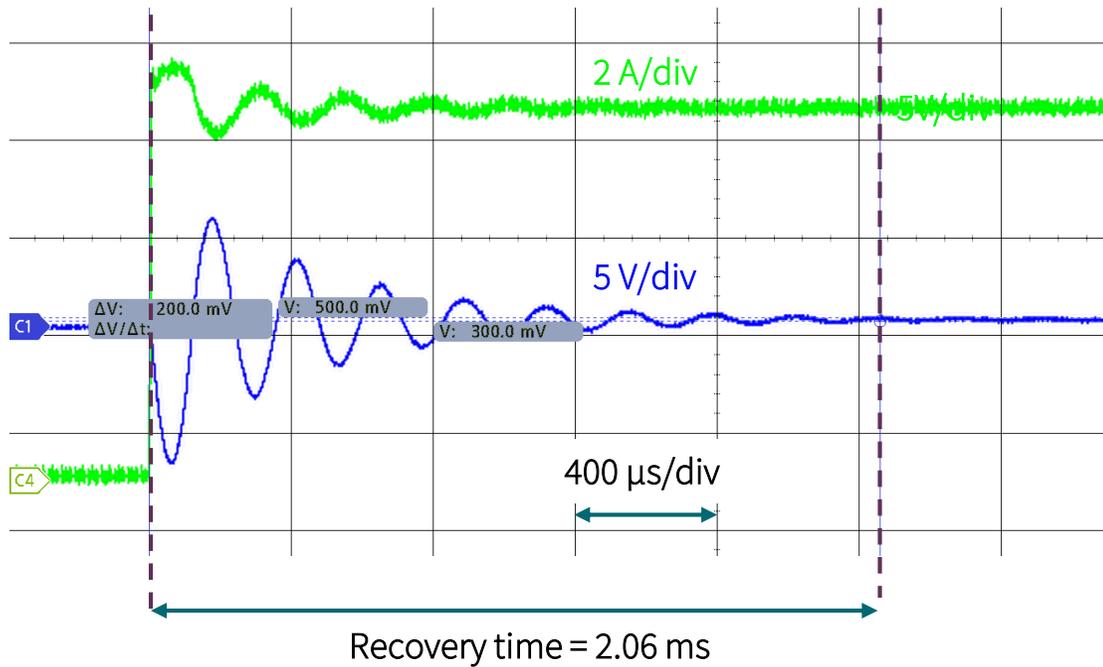
Step response of output voltage

	Dynamic Performance	Specification	Test Result	PASS/FAIL
20 V → 60 V	Rising time	<100us	46.05us	PASS
60 V → 150 V	Rising time	<100us	69.97us	PASS
150 V → 60 V	Falling time	<1ms	0.061ms	PASS
60 V → 20 V	Falling time	<1ms	0.055ms	PASS
20 V → 0 V	Falling time	<1ms	0.044ms	PASS

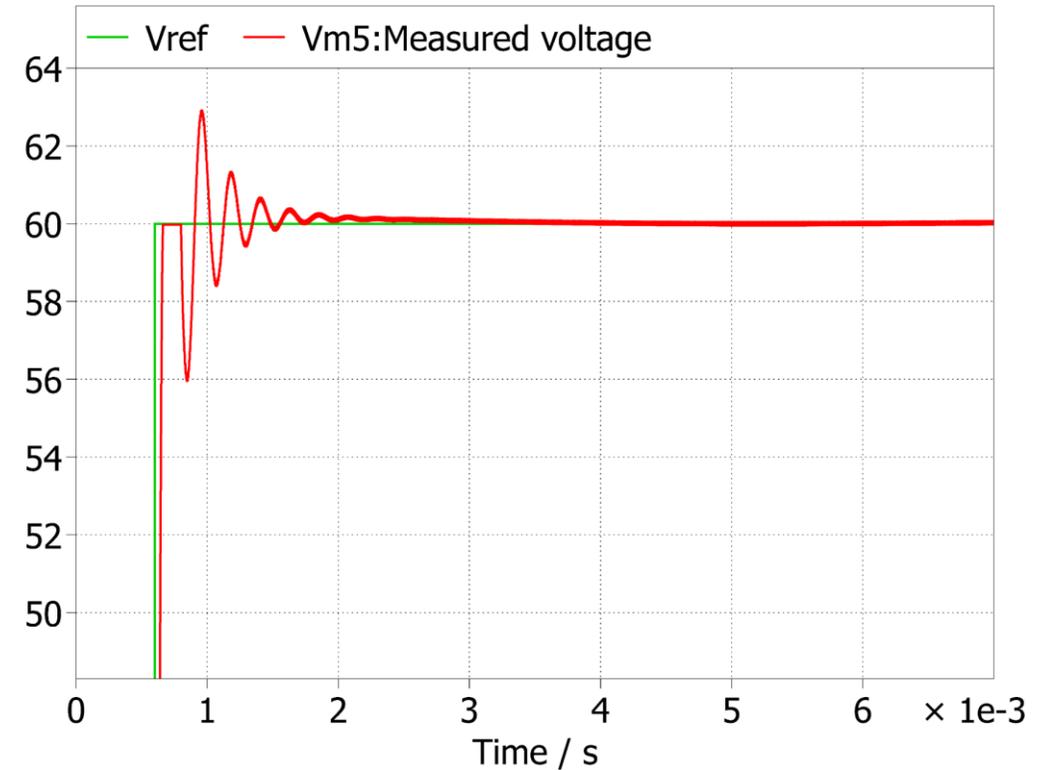


Dynamic performance - load regulation 0 → 10 A

Measurement results

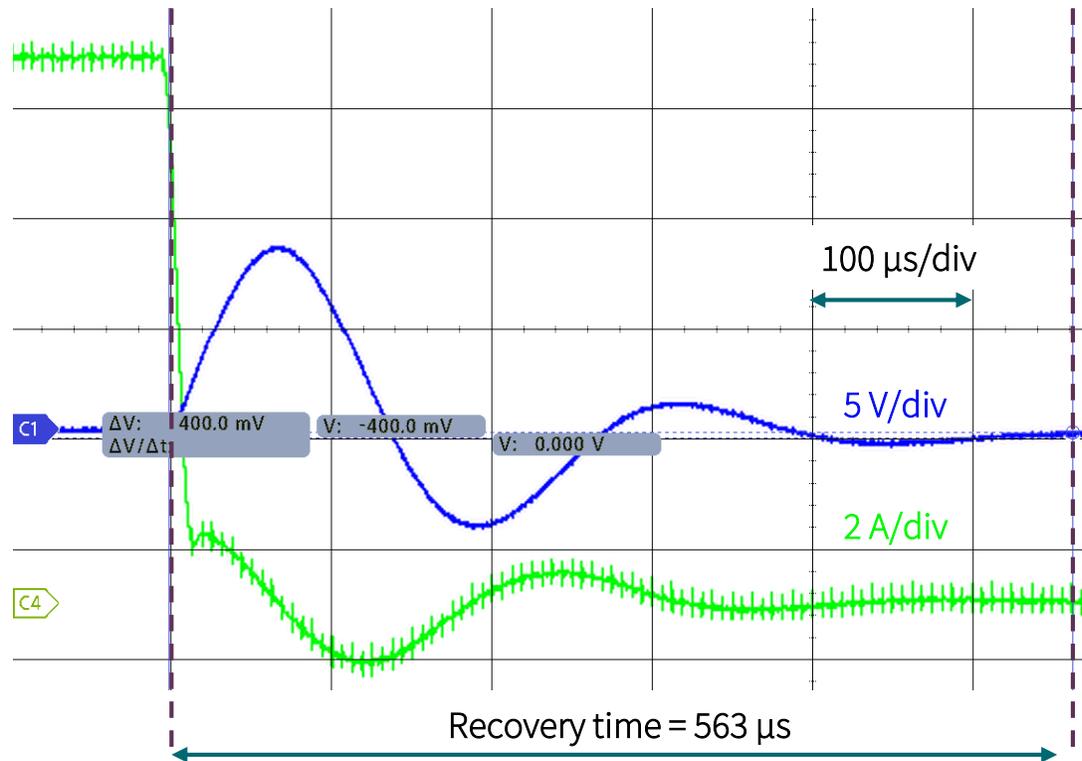


Simulation results



Dynamic performance - load regulation 10 → 0 A

Measurement results



Dynamic performance - load regulation

	Dynamic Performance	Specification	Test Result	PASS/FAIL
20 V, 0 → 10 A	Recovery Time	< 0.1ms	2.06ms	FAIL
20 V, 10 A → 0	Recovery Time	< 0.1ms	0.563ms	FAIL
60 V, 0 → 10 A	Recovery Time	< 0.1ms	1.59ms	FAIL
60 V, 10 A → 0	Recovery Time	< 0.1ms	0.635ms	FAIL
150 V, 0 → 10 A	Recovery Time	< 0.1ms	1.7ms	FAIL
150 V, 10 A → 0	Recovery Time	< 0.1ms	1.712ms	FAIL



Voltage accuracy & load regulation

Voltage Accuracy	Specification	Test Result	PASS/FAIL
No Load	$< \pm 0.5\%$	-0.21% to 0.31%	PASS
Full Load	$< 0.1\%$	-0.06% to 1.42%	FAIL

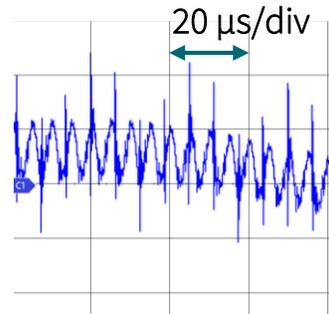
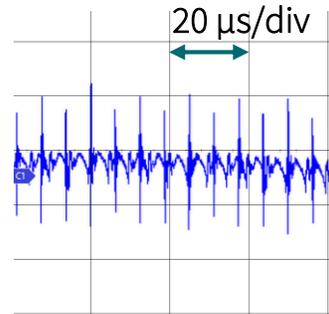
Load Regulation	Specification	Test Result	PASS/FAIL
20V	$< 0.1\%$	-1.3%	FAIL
60V		0.37%	FAIL
150V		-0.26%	FAIL



Voltage noise

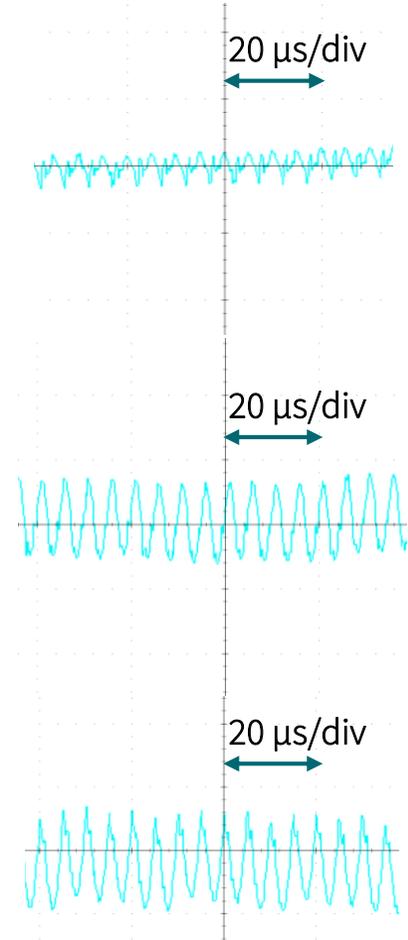
On-site measurement results

Voltage	Test Result
20V	295.9mVp-p
60V	425.5mVp-p
150V	435.1mVp-p



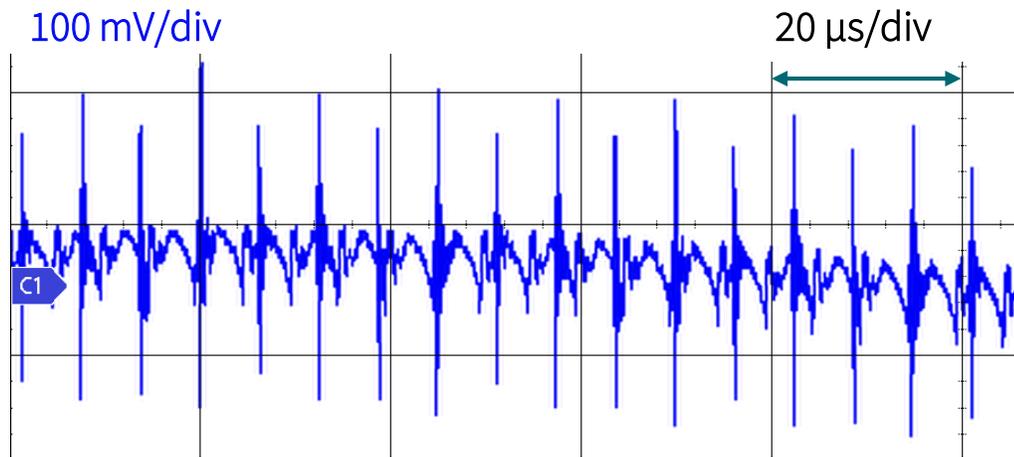
WUT lab results

Voltage	Test Result
20V	73mVp-p
60V	160mVp-p
150V	174mVp-p

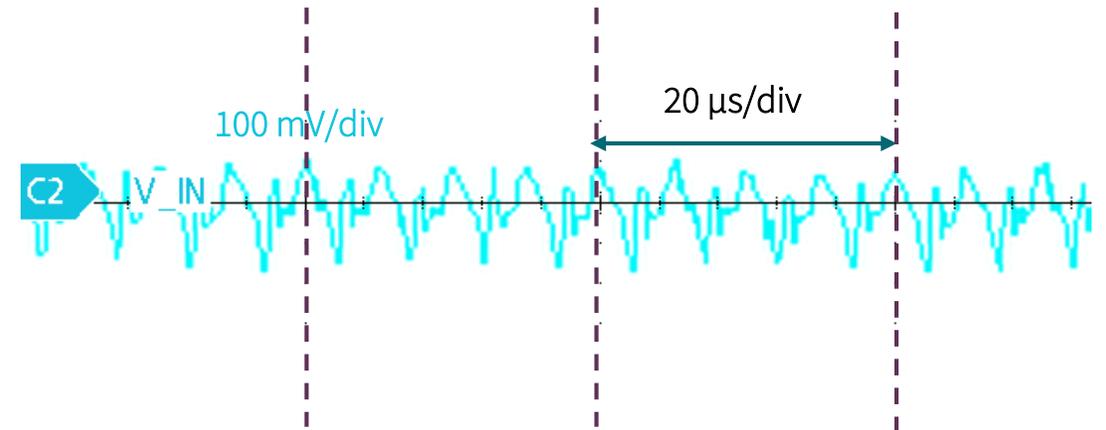


Voltage ripple

IFEC lab results

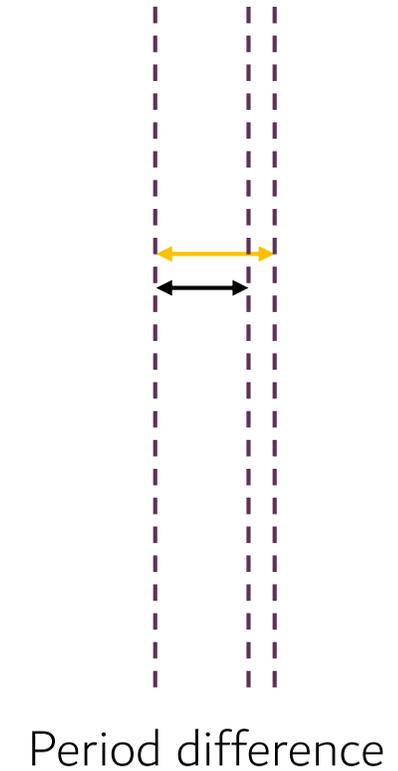
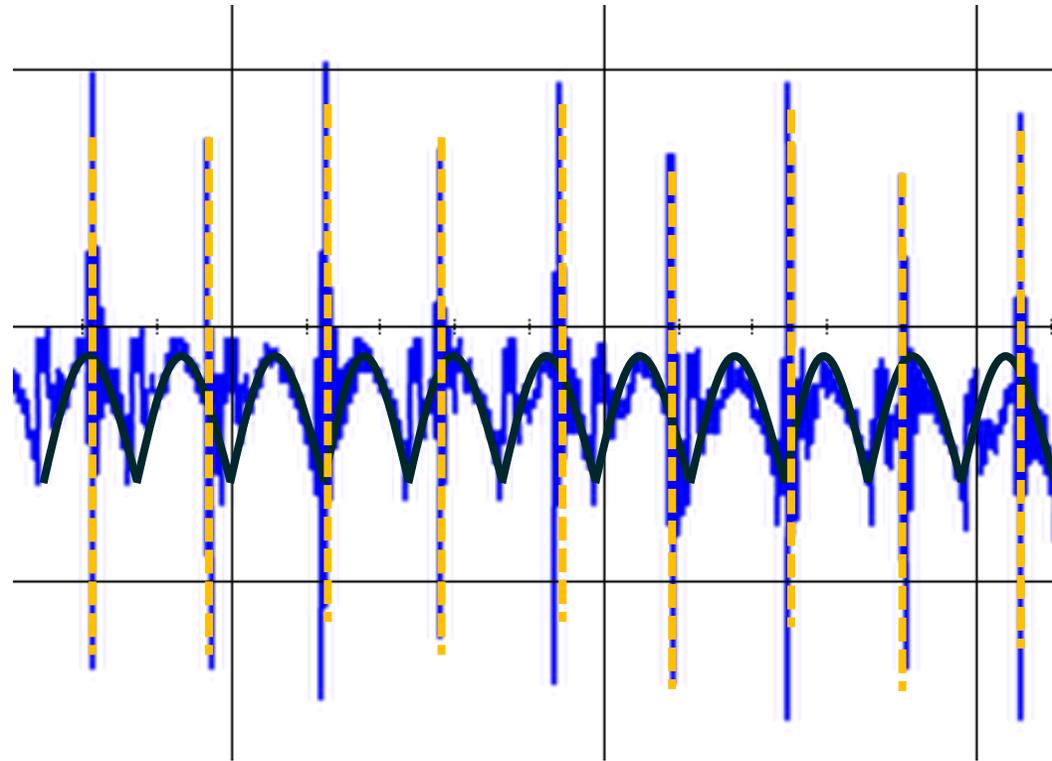


WUT lab results



Voltage ripple

Interference on IFEC noises measurements

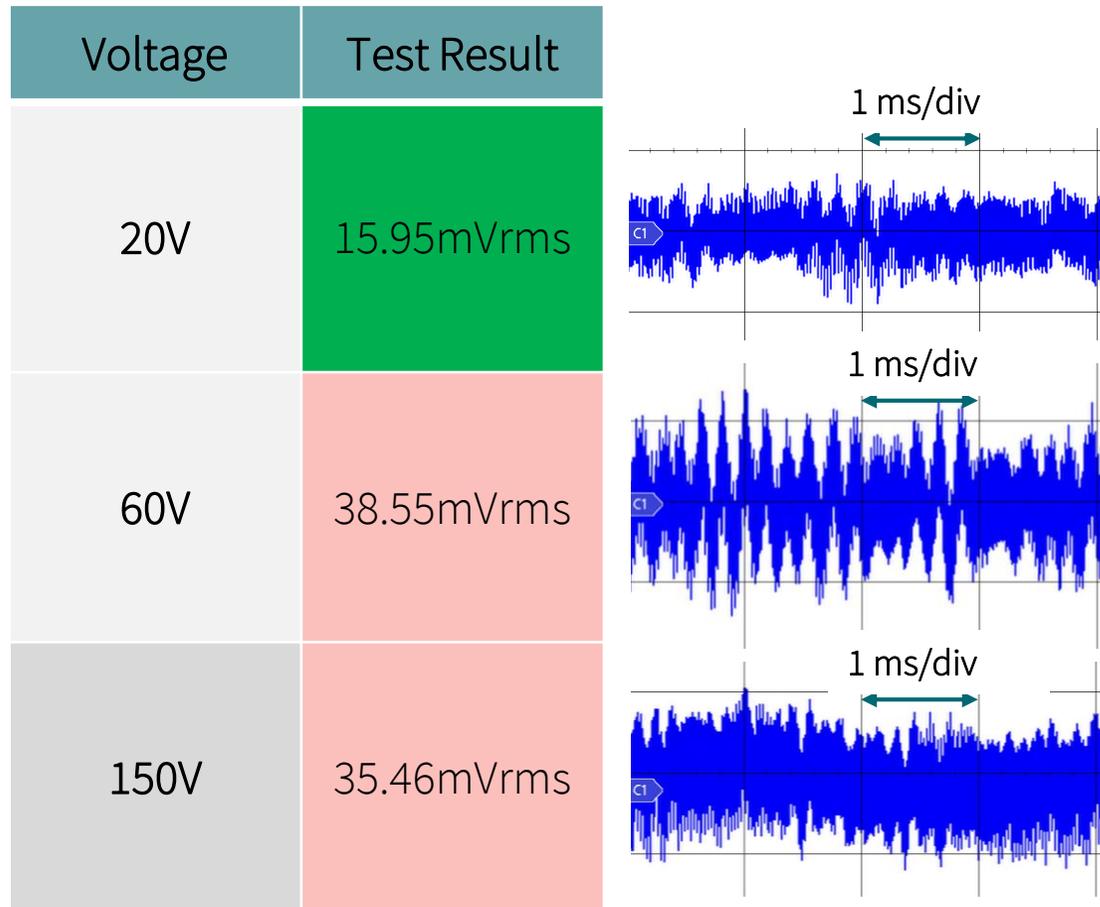


Not our frequency

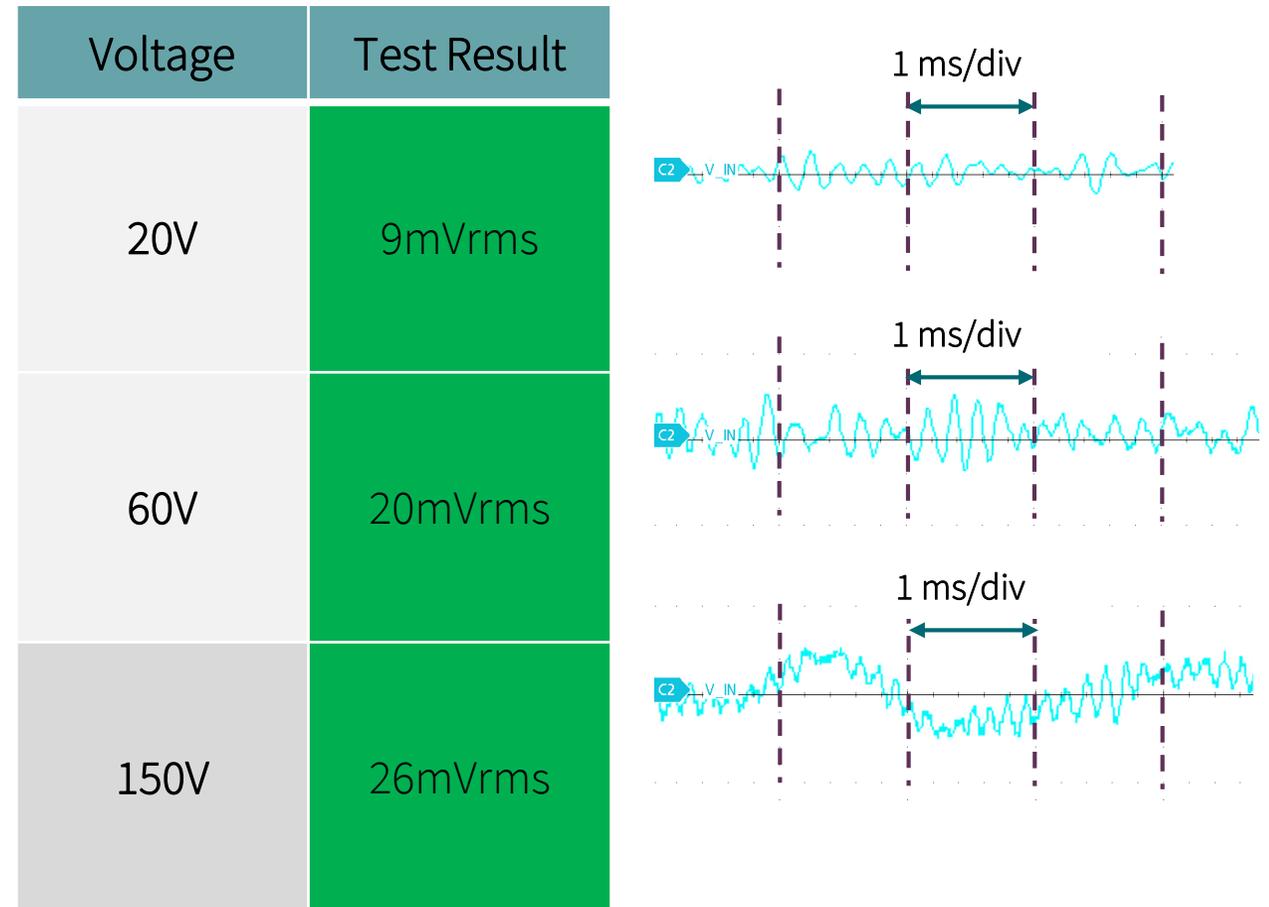


Voltage noise

On-site measurement results



WUT Lab results



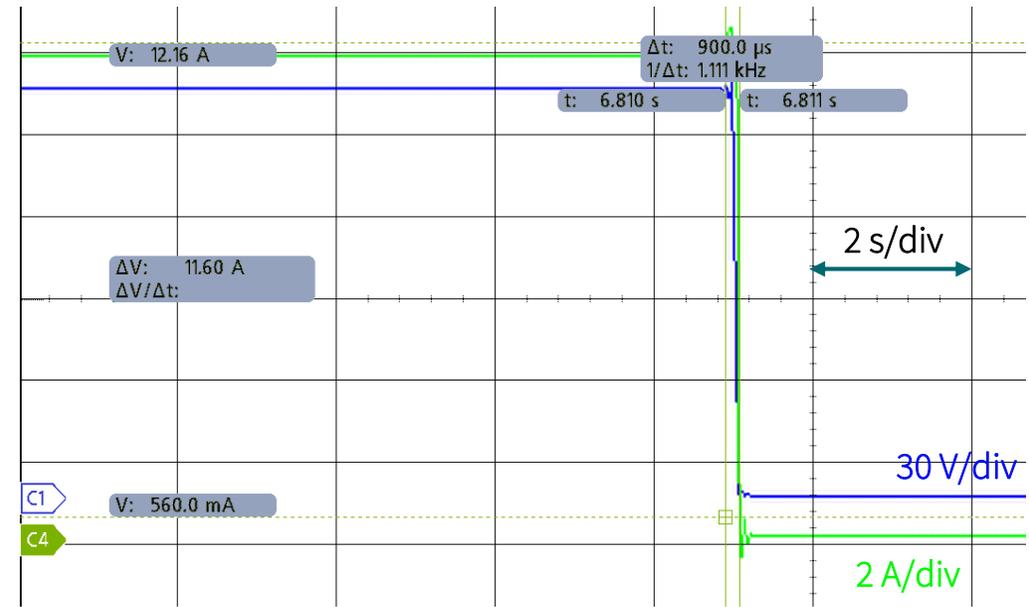
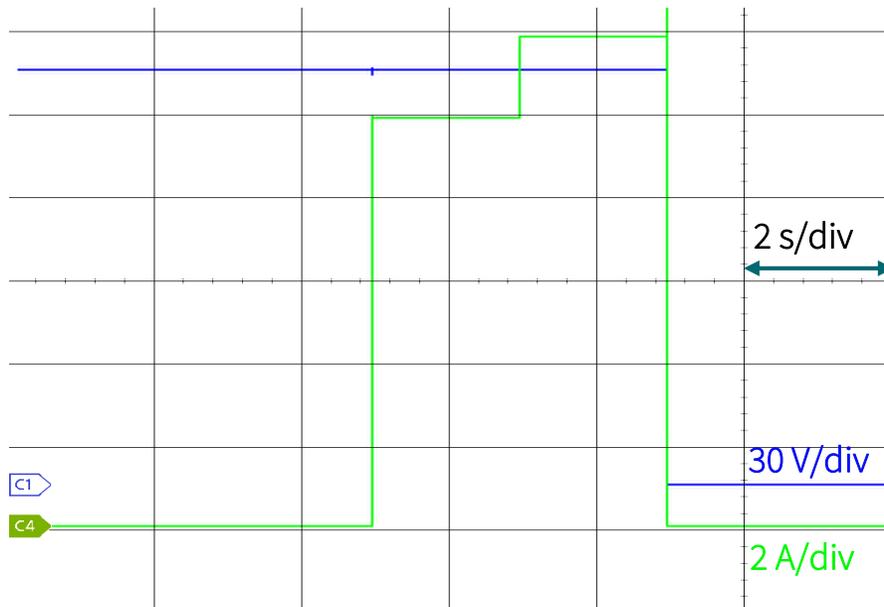
Conversion efficiency

Vo Setting (V)	Load Current Setting (A)	Measurement Output Power Value (W)	Measurement Input Power Value (W)	Conversion Efficiency	Conversion Specification	PASS/FAIL
150	2.5	384.07	400.90	95.80%	> 92%	PASS
	5	762.69	785.33	97.12%	> 96%	PASS
	10	1505.80	1553.90	96.90%	> 95%	PASS



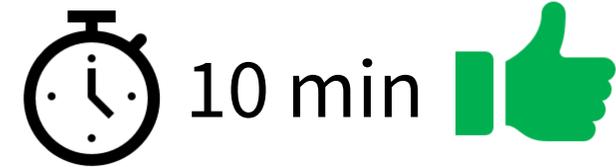
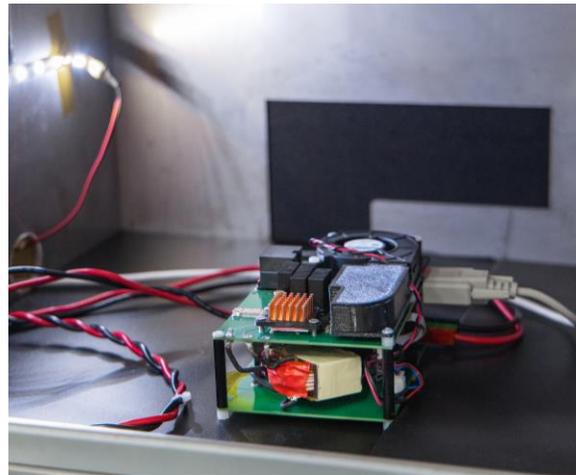
Protection function validation

	Pass Criteria	Test Result	PASS/FAIL
Overload Capability	$P_o = (150V * 12A) \pm 10\%$		PASS
OCP Triggered	< 100ms	900 μ s	
Re-Enable	VDC = 150V \pm 5%		



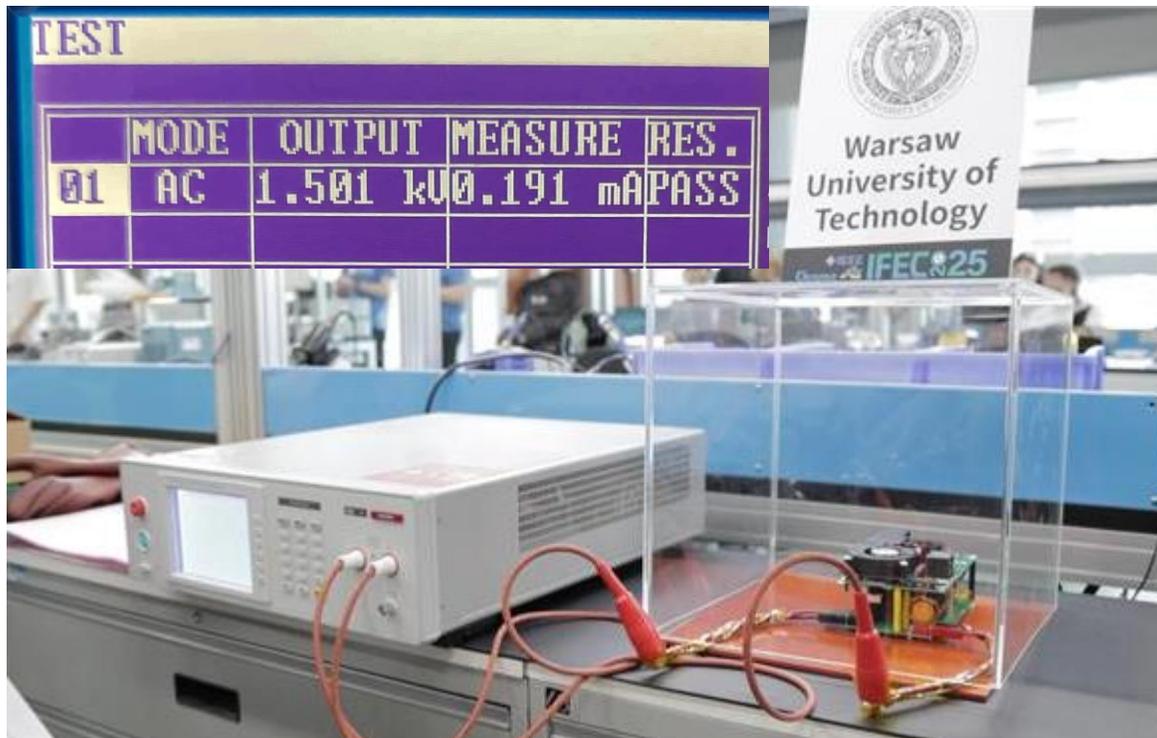
Burn-in test

	Load Condition	Pass Criteria	Test Result
Burn-in Test	Full Load	VDC = 150V \pm 5%, no damage	PASS
	No Load	VDC = 150V \pm 5%, no damage	PASS

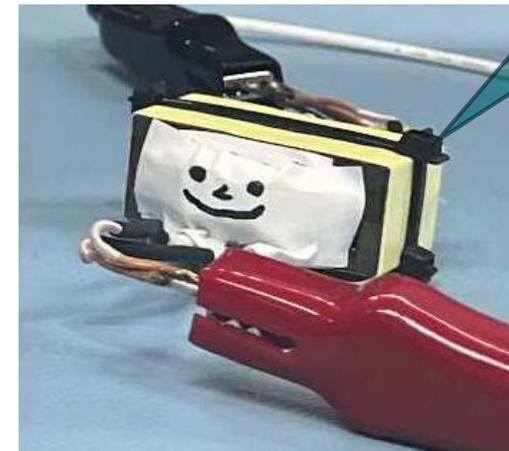


Safety test (Hi-pot test)

	Pass Criteria	Test Result	PASS/FAIL
Leakage Current	< 8mA, no damage	0.191mA	PASS



Lab results

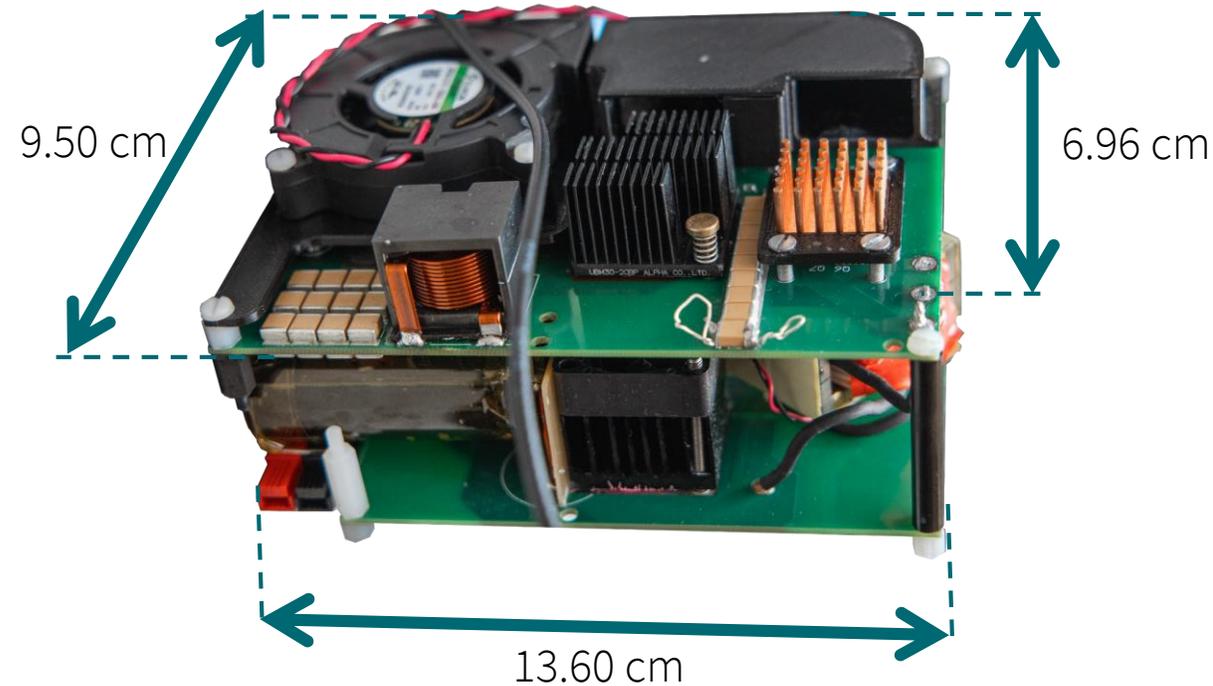


I don't feel anything!



Physical characteristics and design objectives

	Pass Criteria	Test Result	PASS/FAIL
Length	< 30cm	13.60 cm	PASS
Width	< 30cm	9.50 cm	PASS
Height	< 15cm	6.96 cm	PASS
Volume	< 1000 cm ³	898.78 cm ³	PASS
Weight	< 1.5kg	0.585 kg	PASS
Power Density	> 1.6W/cm ³	1.675 W/cm ³	PASS
Weight Density	-	2574.02 W/kg	PASS
Fan noise	< 55dB	32.8dB	PASS



BOM cost breakdown

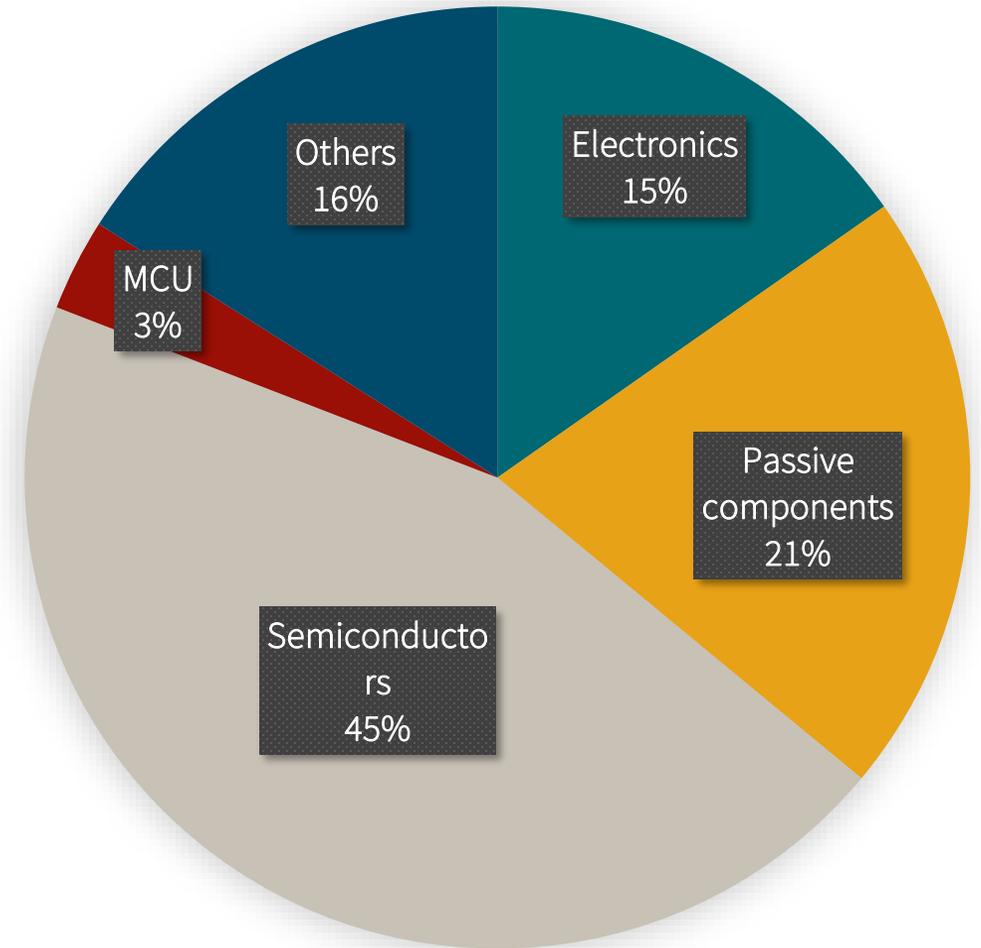
Cost of 1 unit: **\$348.72**

Cost of 1000 units: **\$348,720.00**

	Cost of 1 unit
Semiconductors	\$156.48
Passive components	\$72.44
Others	\$55.64
Electronics	\$53.16
MCU	\$11.00

Prices as of 14 July 2025

Cost distribution



Studencki Ruch Naukowy StRuNa

Nagroda Główna w kategorii StRuNa-TECH





Dziękuję za uwagę

Hardware Design Masterclasses, 28.11.2025

Paweł Wodzyński



Faculty of Electrical Engineering

Warsaw University of Technology